NEC

MOS INTEGRATED CIRCUIT

μPD78011B, 78012B, 78013, 78014

8-BIT SINGLE-CHIP MICROCOMPUTER

DESCRIPTION

The μPD78011B/78012B/78013/78014 are the prodcts in the μPD78014 subseries within the 78K/0 Series.

The μPD78011B/78012B/78013/78014 have 8-bit resolution A/D converter, timer, serial interface, interrupt control, and many other peripheral hardware functions.

A one-time PROM or EPROM product μPD78P014 capable of operating in the same power supply voltage range as of the mask ROM product and other development tools are also provided.

Functions are described in detail in the following User's Manual, which should be read when carring out design work.

μPD78014, 78014Y Series User's Manual: IEU-1343

FEATURES

- Large on-chip ROM & RAM

Item / Product Name	Program Memory (ROM)	Data Memory		Package
		Internal High-Speed RAM	Buffer RAM	
μPD78011B	8K bytes	512 bytes	32 bytes	• 64-pin plastic shrink DIP (750 mil) • 64-pin plastic QFP (□14 mm)
μPD78012B	16K bytes			
μPD78013	24K bytes	1024bytes		
μPD78014	32K bytes			

- External memory expansion space : 64K bytes
- Instruction execution time can be varied from high-speed (0.4 μs) to ultra-low-speed (122 μs)
- I/O ports: 53 (N-ch open-drain : 4)
- 8-bit resolution A/D converter : 8 channels
- Serial interface : 2 channels
- Timer : 5 channels
- Operating voltage range : 2.7 to 6.0 V

Application

Telephone, VCR, audio, camera, home appliances, etc.

The information in this document is subject to change without notice.

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The mark ★ shows major revised points.

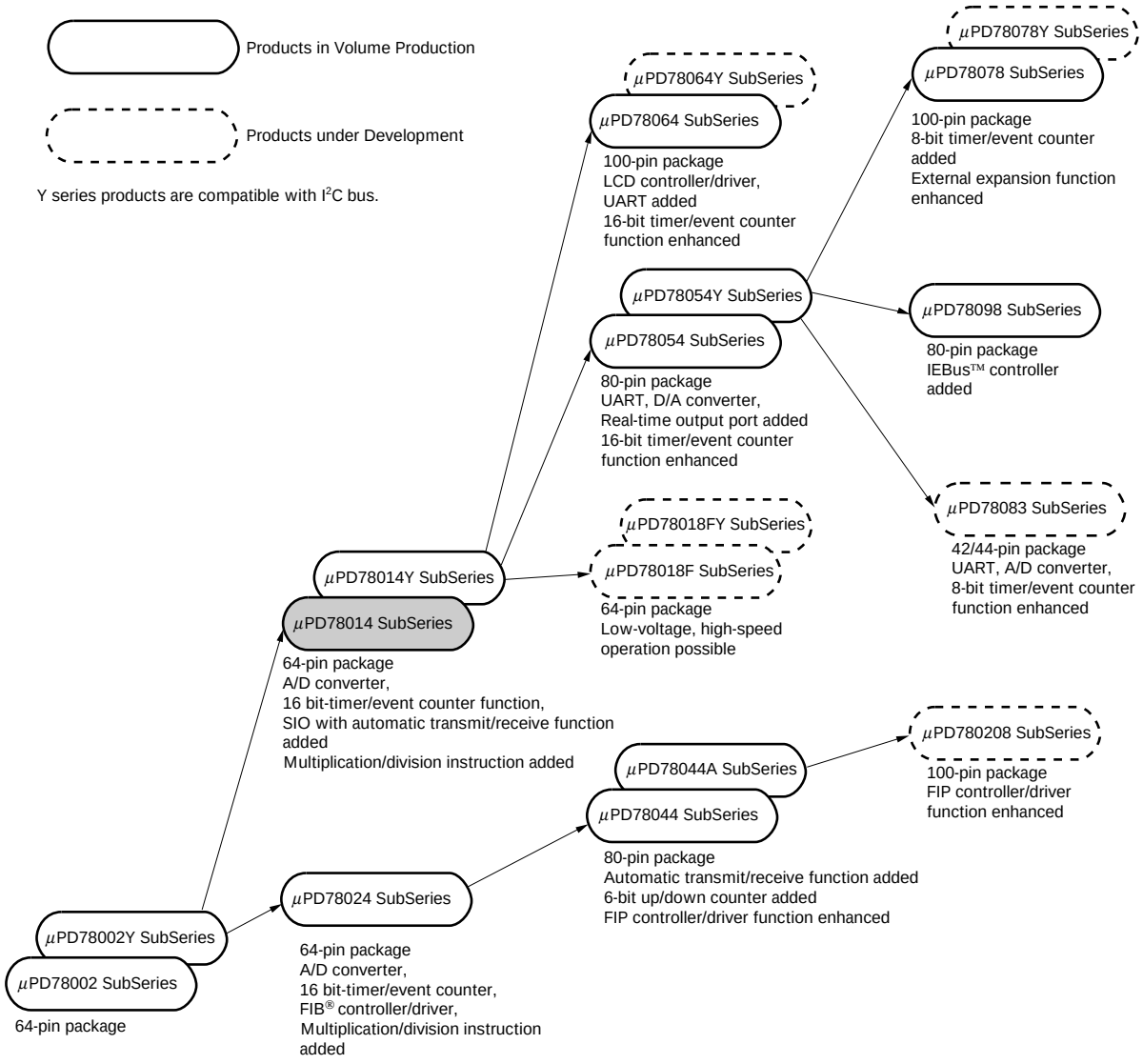
ORDERING INFORMATION

Ordering Code	Package	Quality Grade
μPD78011BCW-×××	64-pin plastic shrink DIP (750 mil)	Standard
μPD78011BGC-×××-AB8	64-pin plastic QFP (□14 mm)	Standard
μPD78012BCW-×××	64-pin plastic shrink DIP (750 mil)	Standard
μPD78012GC-×××-AB8	64-pin plastic QFP (□14 mm)	Standard
μPD78013CW-×××	64-pin plastic shrink DIP (750 mil)	Standard
μPD78013GC-×××-AB8	64-pin plastic QFP (□14 mm)	Standard
μPD78014CW-×××	64-pin plastic shrink DIP (750 mil)	Standard
μPD78014GC-×××-AB8	64-pin plastic QFP (□14 mm)	Standard

Remarks ××× indicates ROM code No.

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

★ 78K/0 SERIES DEVELOPMENT



OVERVIEW OF FUNCTION (1/2)

Item / Product Name		μPD78011B	μPD78012B	μPD78013	μPD78014
Internal memory	ROM	8K bytes	16K bytes	24K bytes	32K bytes
	Internal high-speed RAM	512 bytes		1024 bytes	
	Buffer RAM	32 bytes			
Memory space		64K bytes			
General registers		8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Instruction cycle		On-chip instruction execution time cycle modification function			
	When main system clock selected	0.4 μs/0.8 μs/1.6 μs/3.2 μs/6.4 μs (at 10.0 MHz operation)			
	When subsystem clock selected	122 μs (at 32.768 kHz operation)			
Instruction set		• 16-bit operation • Multiplication/division (8 bits × 8 bits,16 bits ÷ 8 bits) • Bit manipulation (set, reset, test, boolean operation) • BCD correction, etc.			
I/O ports		Total : 53 • CMOS input : 2 • CMOS I/O : 47 • N-channel open-drain I/O (15 V withstand voltage) : 4			
A/D converter		• 8-bit resolution × 8 channels • Operable over a wide power supply voltage range: V_{DD} = 2.7 to 6.0 V			
Serial interface		• 3-wire/SBI/2-wire mode selectable: 1 channel • 3-wire mode (on-chip max. 32 bytes automatic data transmit/receive function): 1 channel			
Timer		• 16-bit timer/event counter : 1 channel • 8-bit timer/event counter : 2 channels • Watch timer : 1 channel • Watchdog timer : 1 channel			
Timer output		3 (14-bit PWM output × 1)			
Clock output		39.1 kHz, 78.1 kHz, 156 kHz, 313 kHz, 625 kHz, 1.25 MHz (at main system clock 10.0 MHz operation), 32.768 kHz (at subsystem clock 32.768 kHz operation)			
Buzzer output		2.4 kHz, 4.9 kHz, 9.8 kHz (at main system clock 10.0 MHz operation)			
Vectored interrupts	Maskable interrupts	Internal : 8 External: 4			
	Non-maskable interrupt	Internal : 1			
	Software interrupt	Internal : 1			

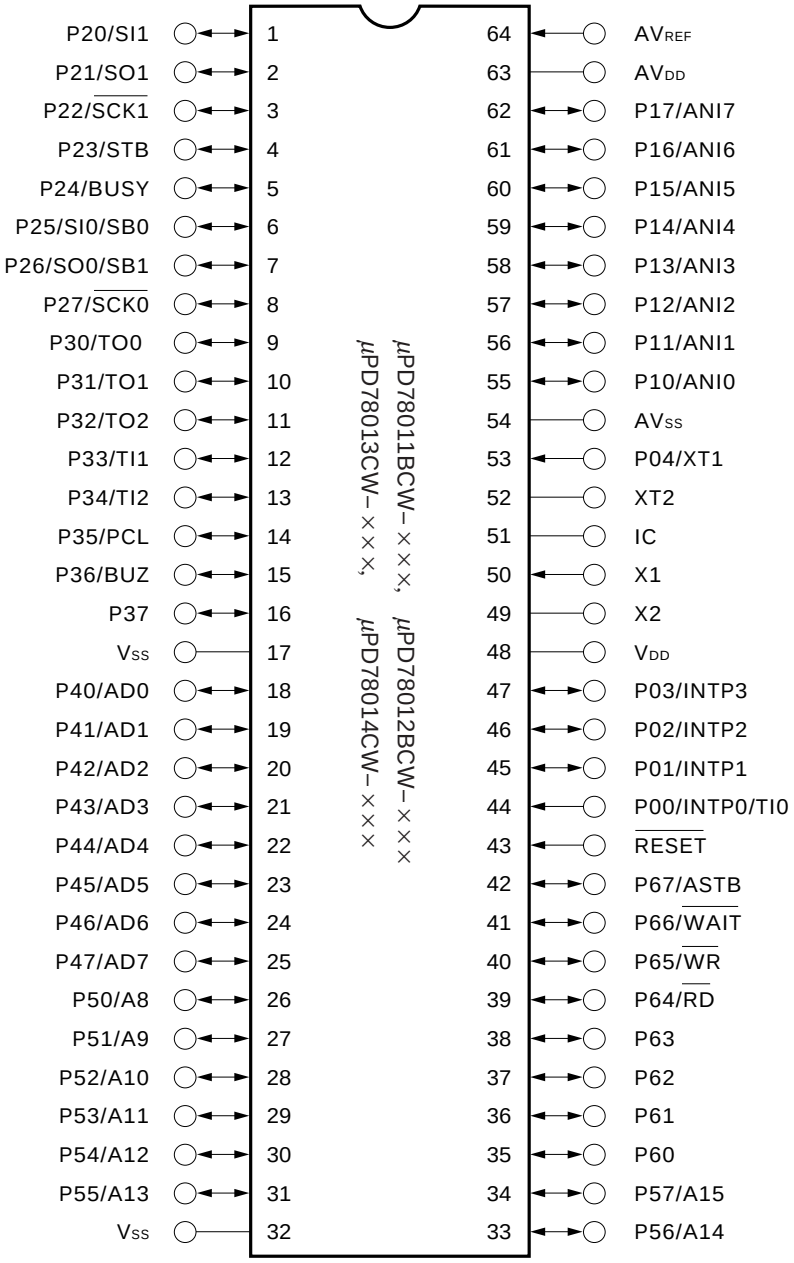
OVERVIEW OF FUNCTION (2/2)

Item / Product Name	μPD78011B	μPD78012B	μPD78013	μPD78014
Test input	Internal : 1 External : 1			
Operating voltage range	V_{DD} = 2.7 to 6.0 V			
Operating temperature range	–40 to +85°C			
Package	• 64-pin plastic shrink DIP (750 mil) • 64-pin plastic QFP (□14 mm)			

CONTENTS

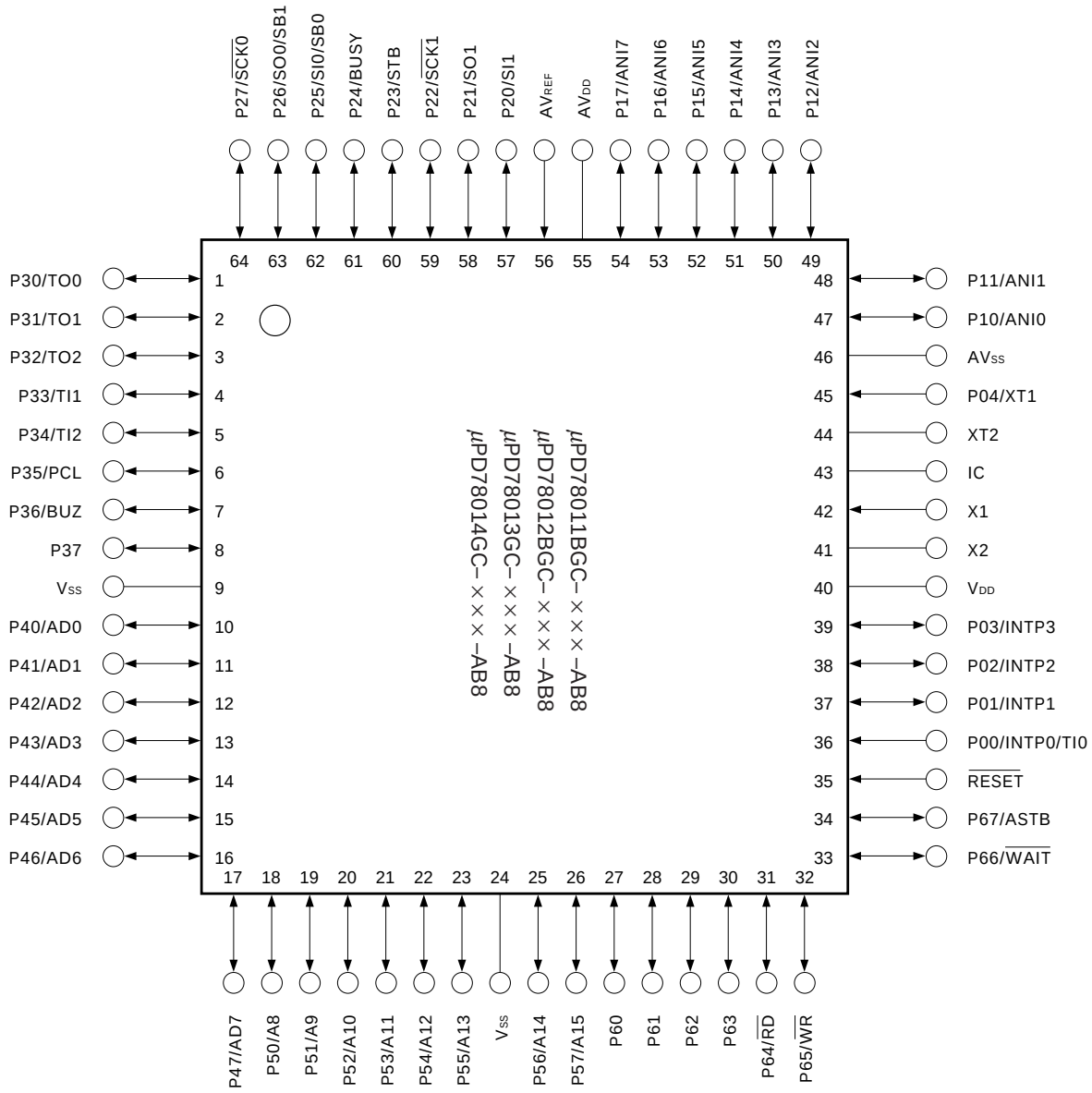
1. PIN CONFIGURATION (Top View)

64-Pin Plastic Shrink DIP (750 mil)



Caution 1. Always connect the IC (Internally Connected) pin to V_{SS} directly.
2. Always connect the AV_{DD} pin to V_{DD}.
3. Always connect the AV_{SS} pin to V_{SS}.

64-Pin Plastic QFP (□14 mm)

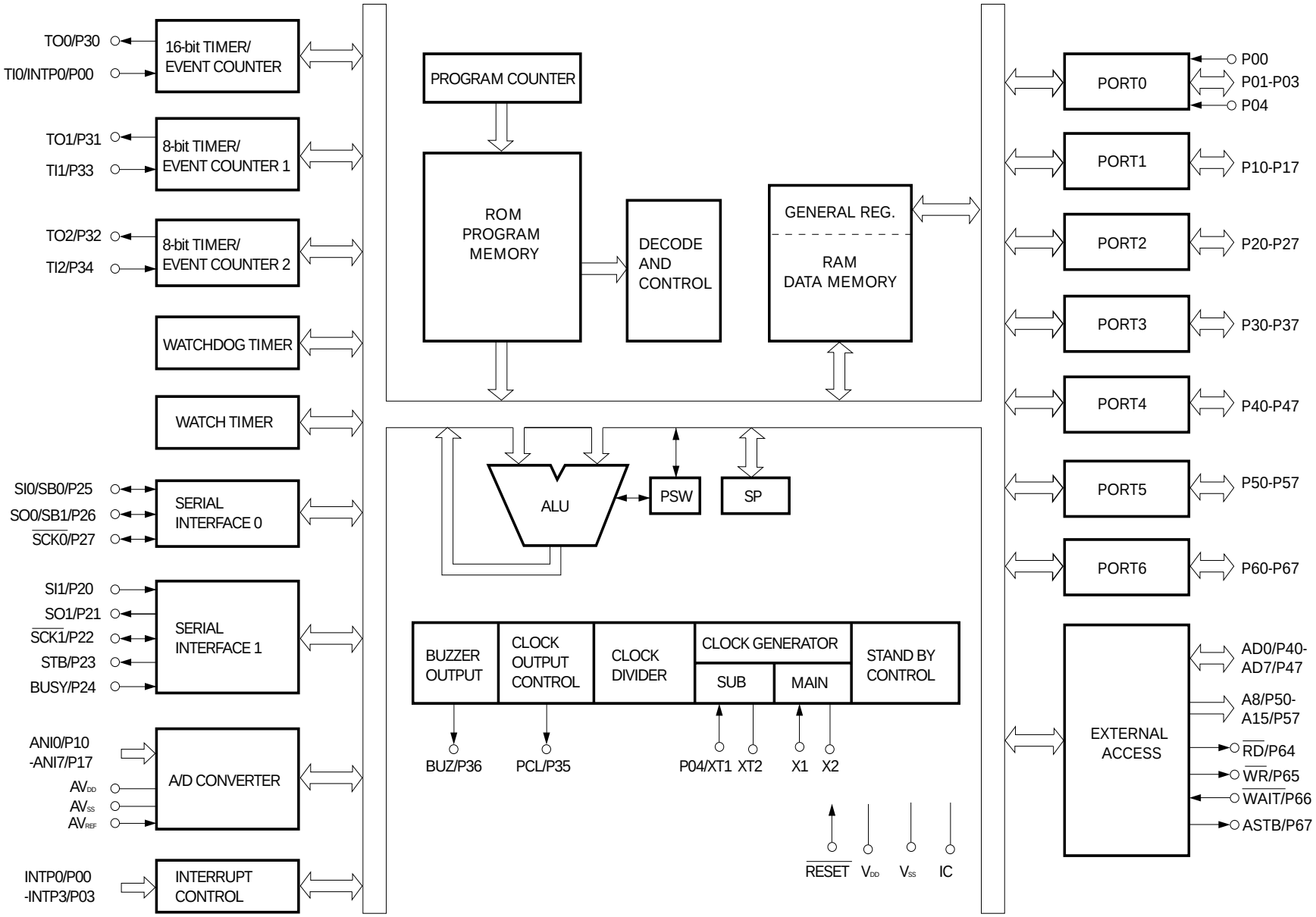


Caution 1. Always connect the IC (Internally Connected) pin to V_{SS} directly.
2. Always connect the AV_{DD} pin to V_{DD}.
3. Always connect the AV_{SS} pin to V_{SS}.

P00 to P04 : Port 0
P10 to P17 : Port 1
P20 to P27 : Port 2
P30 to P37 : Port 3
P40 to P47 : Port 4
P50 to P57 : Port 5
P60 to P67 : Port 6
INTP0 to INTP3 : Interrupt From Peripherals
TI0 to TI2 : Timer Input
TO0 to TO2 : Timer Output
SB0, SB1 : Serial Bus
SI0, SI1 : Serial Input
SO0, SO1 : Serial Output
$\overline{SCK0}$, $\overline{SCK1}$: Serial Clock
PCL : Programmable Clock
BUZ : Buzzer Clock
STB : Strobe
BUSY : Busy

AD0 to AD7 : Address/Data Bus
A8 to A15 : Address Bus
$\overline{RD}$: Read Strobe
$\overline{WR}$: Write Strobe
$\overline{WAIT}$: Wait
ASTB : Address Strobe
X1, X2 : Crystal (Main System Clock)
XT1, XT2 : Crystal (Subsystem Clock)
$\overline{RESET}$: Reset
ANI0 to ANI7 : Analog Input
AV_{DD} : Analog Power Supply
AV_{SS} : Analog Ground
AV_{REF} : Analog Reference Voltage
V_{DD} : Power Supply
V_{SS} : Ground
IC : Internally Connected

2. BLOCK DIAGRAM



Remarks Internal ROM & RAM capacity varies depending on the product.

3. PIN FUNCTIONS

3.1 PORT PINS (1/2)

Pin Name	I/O	Function		After Reset	Dual-Function Pin
P00	Input	Port 0 5-bit I/O port	Input only	Input	INTP0/TI0
P01	Input/output		Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.	Input	INTP1
P02					INTP2
P03					INTP3
P04***1**	Input		Input only	Input	XT1
P10 to P17	Input/output	Port 1 8-bit input/output port. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.***2**		Input	ANI0 to ANI7
P20	Input/output	Port 2 8-bit input/output port. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.		Input	SI1
P21					SO1
P22					$\overline{\text{SCK1}}$
P23					STB
P24					BUSY
P25					SI0/SB0
P26					SO0/SB1
P27					$\overline{\text{SCK0}}$
P30	Input/output	Port 3 8-bit input/output port. Input/output can be specified in 1-bit units. When used as an input port, pull-up resistor can be used by software.		Input	TO0
P31					TO1
P32					TO2
P33					TI1
P34					TI2
P35					PCL
P36					BUZ
P37					—
P40 to P47	Input/output	Port 4 8-bit input/output port. Input/output can be specified in 8-bit unit. When used as an input port, pull-up resistor can be used by software. Test input flag (KRIF) is set to 1 by falling edge detection.		Input	AD0 to AD7

*** 1.** When using the P04/XT1 pins as an input port, set 1 to bit 6 (REC) of the processor control register. Do not use the on-chip feedback register of the subsystem clock oscillator.

2. When using the P10/ANI0 to P17/ANI7 pins as the A/D converter analog input, pull-up resistor is automatically unused.

3.1 PORT PINS (2/2)

Pin Name	I/O	Function		After Reset	Dual-Function Pin
P50 to P57	Input/output	Port 5 8-bit input/output port. LED can be driven directly. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.		Input	A8 to A15
P60	Input/output	Port 6 8-bit input/output port. Input/output can be specified bit-wise.	N-ch open-drain input/output port. On-chip pull-up resistor can be specified by mask option. LED can be driven directly.	Input	———
P61					
P62					
P63					
P64			When used as an input port, pull-up resistor can be used by software.		$\overline{RD}$
P65					$\overline{WR}$
P66					$\overline{WAIT}$
P67					ASTB

Caution When pull-up resistors are not used (specified by mask option), the low-level input leak current increases with -200 μA (MAX.) under either of the following conditions.

① When the external device expansion function is used and a low-level is input to the pin.
② During the 3-clock period when a read instruction is executed on port 6 (P6) and the port mode register (PM6).

3.2 OTHER PORTS (1/2)

Pin Name	I/O	Function	After Reset	Dual-Function Pin
INTP0	Input	External interrupt input by which the effective edge (rising edge, falling edge, or both rising edge and falling edge) can be specified.	Input	P00/TI0
INTP1				P01
INTP2				P02
INTP3		Falling edge detection external interrupt input.		P03
SI0	Input	Serial interface serial data input.	Input	P25/SB0
SI1				P20
SO0	Output	Serial interface serial data output.	Input	P26/SB1
SO1				P21
SB0	Input/output	Serial interface serial data input/output.	Input	P25/SI0
SB1				P26/SO0
$\overline{SCK0}$	Input/output	Serial interface serial clock input/output.	Input	P27
$\overline{SCK1}$				P22
STB	Output	Serial interface automatic transmit/receive strobe output.	Input	P23
BUSY	Input	Serial interface automatic transmit/receive busy input.	Input	P24

3.2 OTHER PORTS (2/2)

Pin Name	I/O	Function	After Reset	Dual-Function Pin
TI0	Input	External count clock input to 16-bit timer (TM0).	Input	P00/INTP0
TI1		External count clock input to 8-bit timer (TM1).		P33
TI2		External count clock input to 8-bit timer (TM2).		P34
TO0	Output	16-bit timer output (shared as 14-bit PWM output).	Input	P30
TO1		8-bit timer output.		P31
TO2				P32
PCL	Output	Clock output (for main system clock, subsystem clock trimming).	Input	P35
BUZ	Output	Buzzer output.	Input	P36
AD0 to AD7	Input /output	Low-order address/data bus at external memory expansion.	Input	P40 to P47
A8 to A15	Output	High-order address bus at external memory expansion.	Input	P50 to P57
$\overline{RD}$	Output	External memory read operation strobe signal output.	Input	P64
$\overline{WR}$		External memory write operation strobe signal output.		P65
$\overline{WAIT}$	Input	Wait insertion at external memory access.	Input	P66
ASTB	Output	Strobe output which latches the address information output at port 4 and port 5 to access external memory.	Input	P67
ANI0 to ANI7	Input	A/D converter analog input.	Input	P10 to P17
AV_{REF}	Input	A/D converter reference voltage input.	—	—
AV_{DD}	—	A/D converter analog power supply. Connected to V_{DD}.	—	—
AV_{SS}	—	A/D converter ground potential. Connected to V_{SS}.	—	—
$\overline{RESET}$	Input	System reset input.	—	—
X1	Input	Main system clock oscillation crystal connection.	—	—
X2	—		—	—
XT1	Input	Subsystem clock oscillation crystal connection.	Input	P04
XT2	—		—	—
V_{DD}	—	Positive power supply.	—	—
V_{SS}	—	Ground potential.	—	—
IC	—	Internal connection. Connected to V_{SS} directly.	—	—

3.3 PIN I/O CIRCUITS AND RECOMMENDED CONNECTION OF UNUSED PINS

The input/output circuit type of each pin and recommended connection of unused pins are shown in Table 3-1.

For the input/output circuit configuration of each type, see Fig. 3-1.

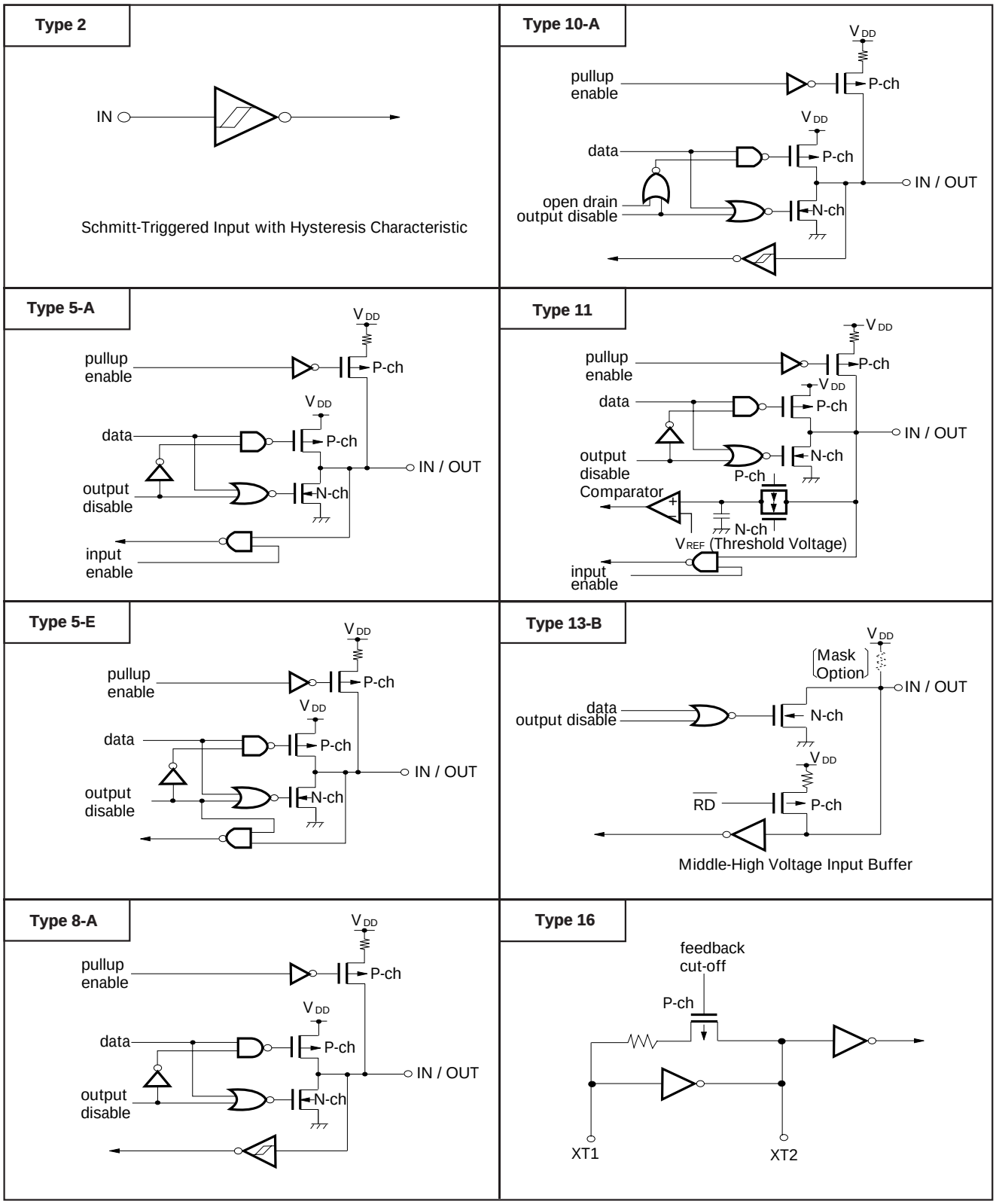
Table 3-1 Input/Output Circuit Type of Each Pin (1/2)

Pin Name	Input/output Circuit Type	I/O	Recommended Connection when Not Used
P00/INTP0/TI0	2	Input	Connected to V_{SS}.
P01/INTP1	8-A	Input/output	Input : Connected to V_{SS}. Output : Leave open.
P02/INTP2			
P03/INTP3			
P04/XT1	16	Input	Connected to V_{SS}.
P10/ANI0 to P17/ANI7	11	Input/output	Input : Connected to V_{DD} or V_{SS}. Output : Leave open.
P20/SI1	8-A	Input/output	Input : Connected to V_{DD} or V_{SS}. Output : Leave open.
P21/SO1	5-A		
P22/$\overline{SCK1}$	8-A		
P23/STB	5-A		
P24/BUSY	8-A		
P25/SI0/SB0	10-A		
P26/SO0/SB1			
P27/$\overline{SCK0}$			
P30/TO0	5-A	Input/output	Input : Connected to V_{DD} or V_{SS}. Output : Leave open.
P31/TO1			
P32/TO2			
P33/TI1	8-A		
P34/TI2			
P35/PCL	5-A		
P36/BUZ			
P37			
P40/AD0 to P47/AD7	5-E	Input/output	Input : Connected to V_{DD} or V_{SS}. Output : Leave open.
P50/A8 to P57/A15	5-A	Input/output	Input : Connected to V_{DD} or V_{SS}. Output : Leave open.
P60 to P63	13-B		
P64/$\overline{RD}$	5-A		
P65/$\overline{WR}$			
P66/$\overline{WAIT}$			
P67/ASTB			

Table 3-1 Input/Output Circuit Type of Each Pin (2/2)

Pin Name	Input/Output Circuit Type	I/O	Recommended Connection when Not Used
$\overline{\text{RESET}}$	2	Input	—
XT2	16	—	Leave open.
AV_{REF}	—		Connected to V_{SS}.
AV_{DD}			Connected to V_{DD}.
AV_{SS}			Connected to V_{SS}.
IC			Connected to V_{SS} directly.

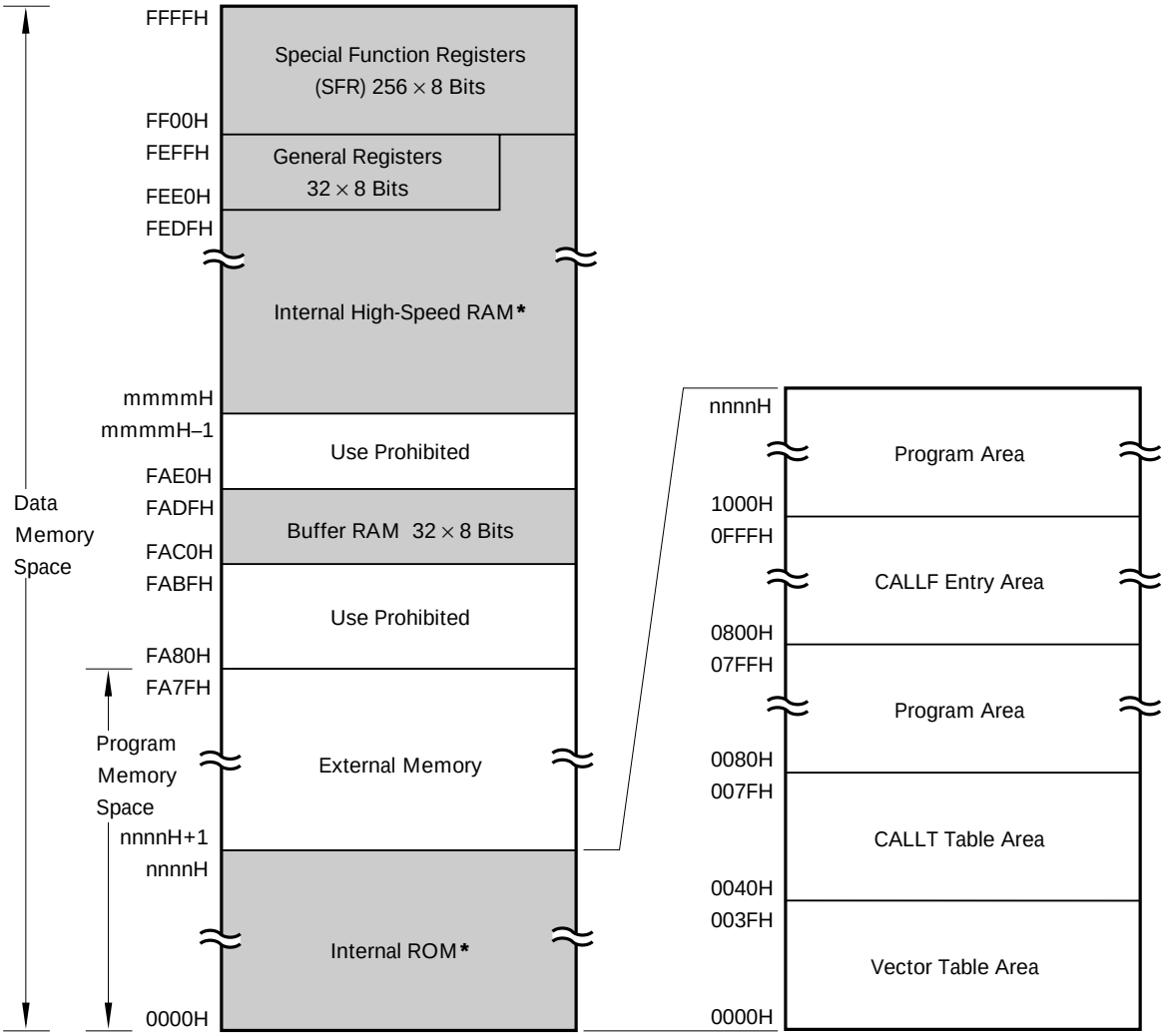
Fig. 3-1 Pin Input/Output Circuits



4. MEMORY SPACE

The memory map of μPD78011B/78012B/78013/78014 is shown in Fig 4-1.

Fig.4-1 Memory Map



Remarks Shaded area indicates internal memory.

* Intermal ROM and internal high-speed RAM capacities vary depending on the product (see the table below).

Product Name	Intenal ROM End Address nnnnH	Internal High-Speed RAM StartAddress mmmmH
μPD78011B	1FFFH	FD00H
μPD78012B	3FFFH	
μPD78013	5FFFH	FB00H
μPD78014	7FFFH	

5 PERIPHERAL HARDWARE FUNCTION FEATURES

5.1 PORTS

The I/O port has the following three types

- CMOS input (P00, P04) : 2
- CMOS input/output (P01 to P03, port 1 to port 5, P64 to P67) : 47
- N-ch open-drain input/output(15V withstand voltage) (P60 to P63) : 4

Total : 53

Table 5-1 Functions of Ports

Port Name	Pin Name	Function
Port 0	P00, P04	Dedicated Input port
	P01 to P03	Input/output ports. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.
Port 1	P10 to P17	Input/output ports. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.
Port 2	P20 to P27	Input/output ports. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.
Port 3	P30 to P37	Input/output ports. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.
Port 4	P40 to P47	Input/output ports. Input/output can be specified in 8-bit units. When used as an input port, pull-up resistor can be used by software. Test input flag (KRIF) is set to 1 by falling edge detection.
Port 5	P50 to P57	Input/output ports. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software. LED can be driven directly.
Port 6	P60 to P63	N-ch open-drain input/output port. Input/output can be specified bit-wise. On-chip pull-up resistor can be specified by mask option. LED can be driven directly.
	P64 to P67	Input/output ports. Input/output can be specified bit-wise. When used as an input port, pull-up resistor can be used by software.

Caution When pull-up resistors are not used (specified by mask option), low-level input leak current increases with – 200 *m*A (MAX.) under either of the following conditions.

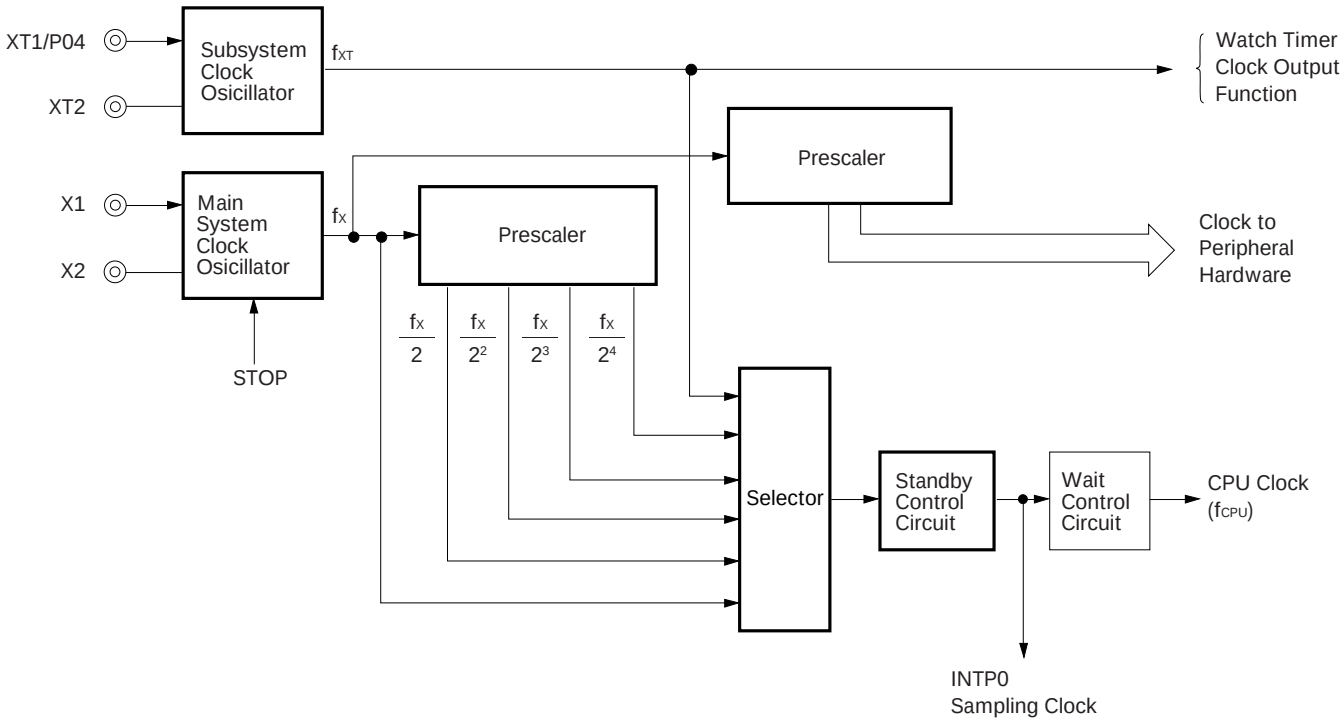
① When the external device expansion function is used and a low-level is input to the pin.
② During the 3-clock period when a read instruction is executed on port 6 (P6) and the port mode register (PM6).

5.2 CLOCK GENERATOR

There are two types of clock generator: main system clock and subsystem clock.
The instruction exection time can be changed.

- 0.4μs/0.8μs/1.6μs/3.2μs/6.4μs (Main system clock: at 10.0 MHz operation)
- 122μs (Subsystem clock: at 32.768 KHz operation)

Fig. 5-1 Clock Generator Block Diagram



5.3 TIMER/EVENT COUNTER

The following five channels are incorporated in the timer/event counter.

- 16-bit timer/event counter : 1 channel
- 8-bit timer/event counter : 2 channels
- Watch timer : 1 channel
- Watchdog timer : 1 channel

Table 5-2 Types and Features of Timer/Event Counter

		16-bit Timer/Event Counter	8-bit Timer/Event Counter	Watch Timer	Watchdog Timer
Type	Interval timer	1 channel	2 channels	1channel	1 channel
	Externanal event counter	1 channel	2 channels	–	–
Functions	Timer output	1 output	2 outputs	–	–
	PWM output	1 output	–	–	–
	Pulse width mesurement	1 input	–	–	–
	Sqare wave output	1 output	2 outputs	–	–
	Interrupt request	2	2	2	1

Fig. 5-2 16-bit Timer/Enent Counter Block Diagram

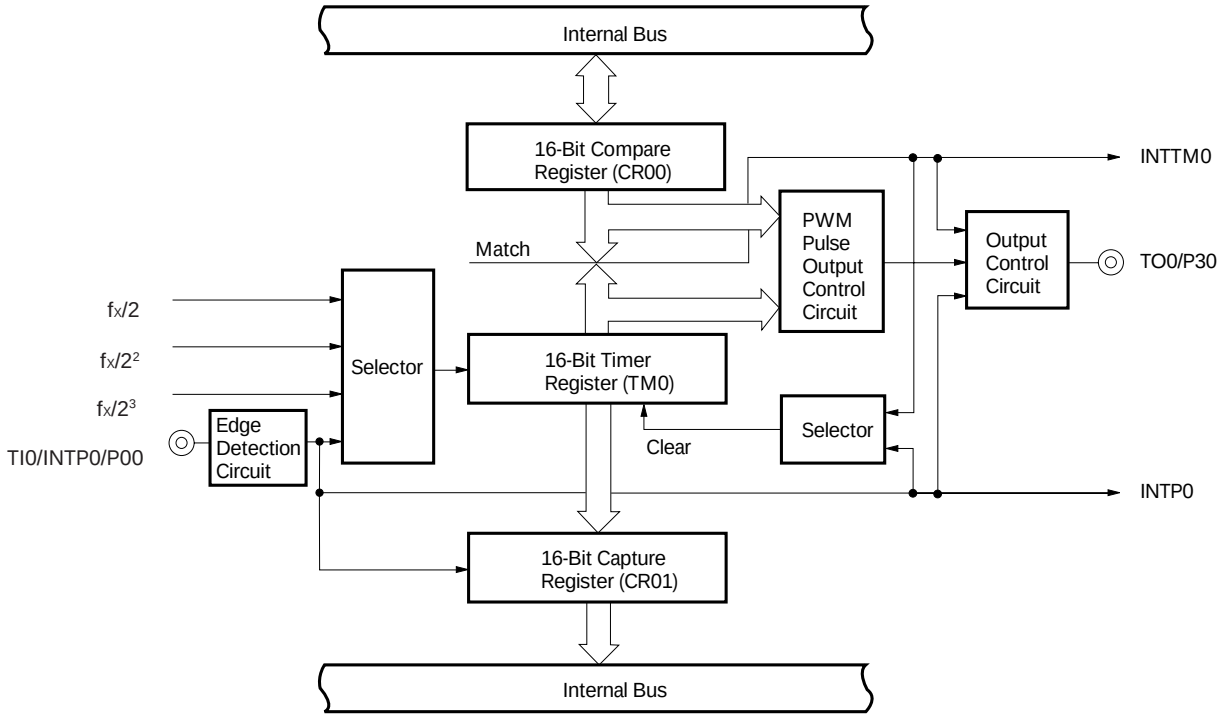


Fig. 5-3 8-bit Timer/Enent Counter Block Diagram

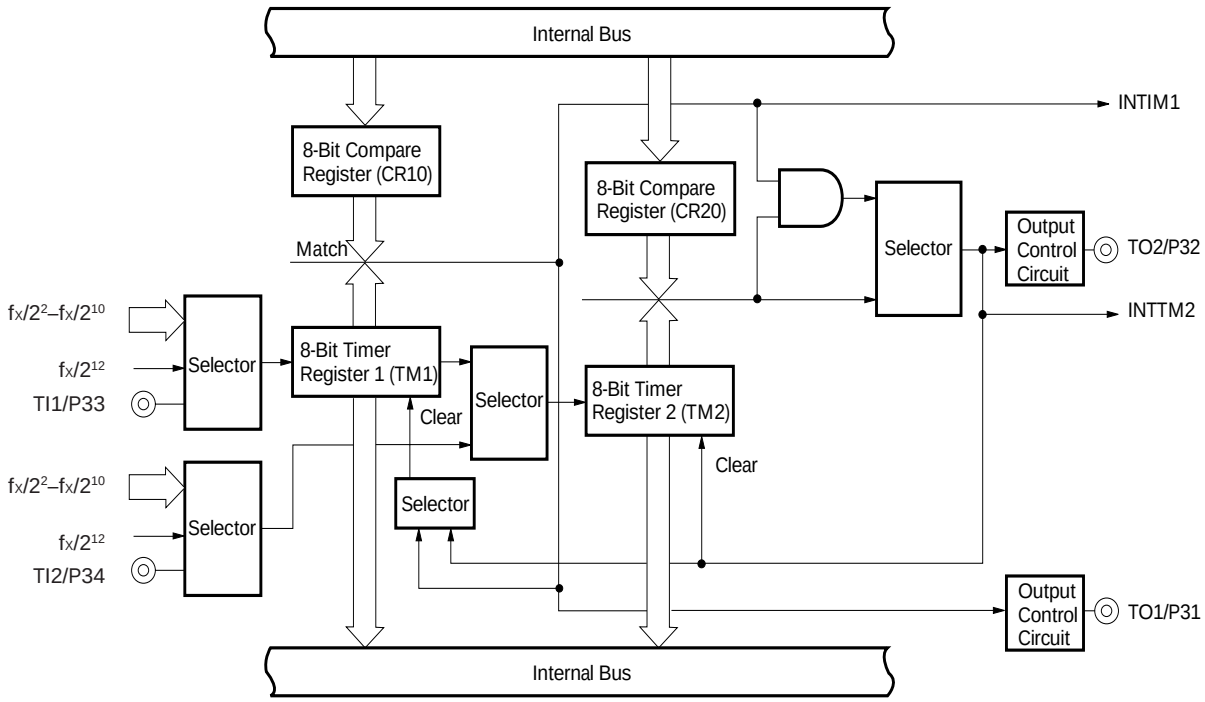


Fig. 5-4 Watch Timer Block Diagram

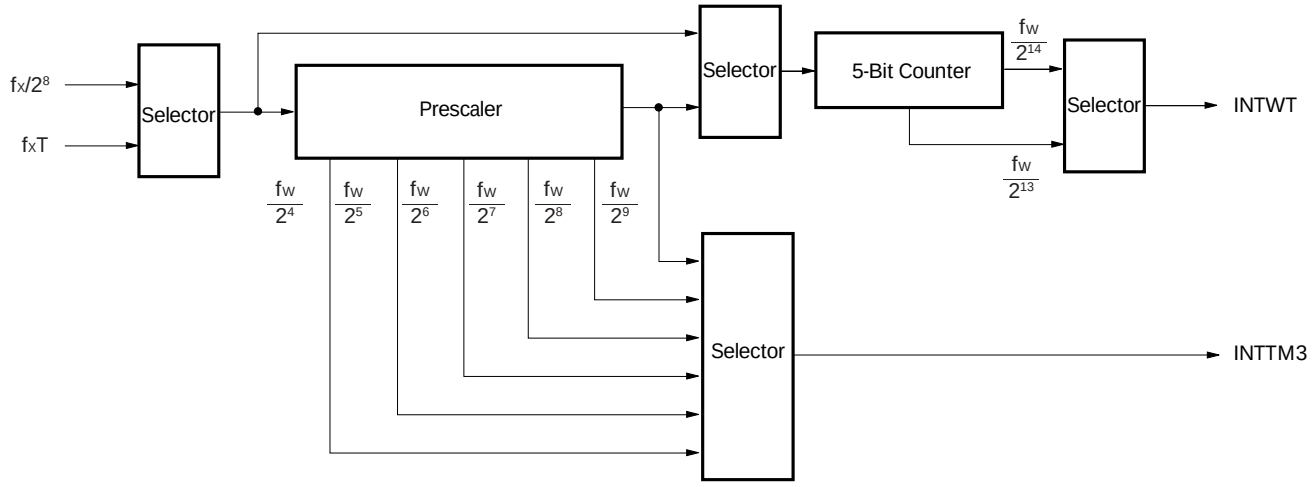
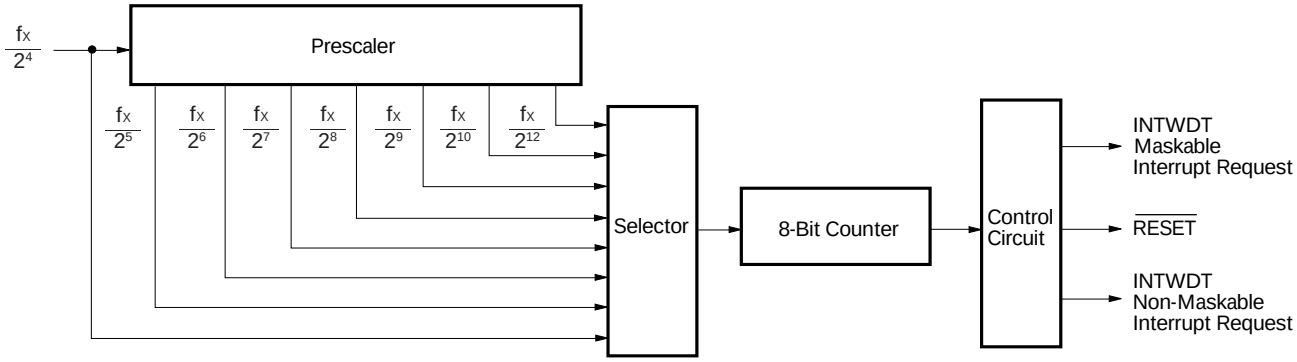


Fig. 5-5 Watchdog Timer Block Diagram

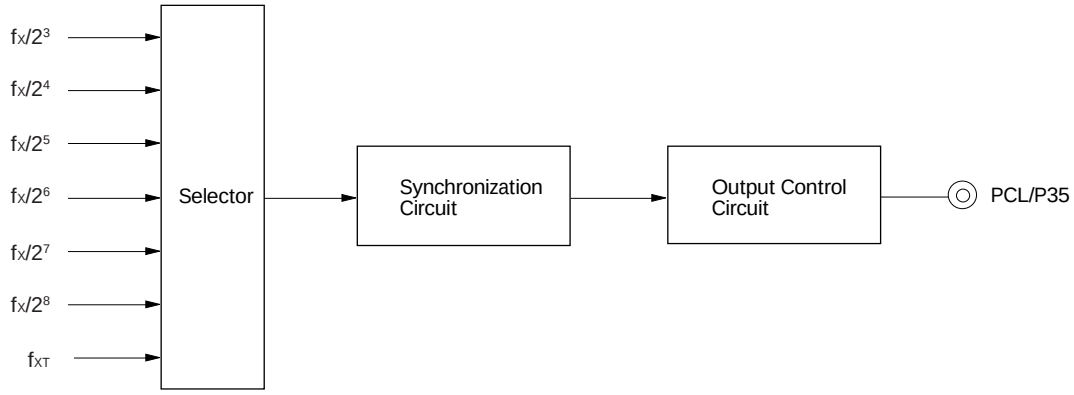


5.4 CLOCK OUTPUT CONTROL CIRCUIT

The clock with the following frequencies can be output for clock output.

- 39.1 kHz/78.1 kHz/156 kHz/313 kHz/625 kHz/1.25 MHz (Main system clock: at 10.0 MHz operation)
- 32.768 kHz (Subsystem clock: at 32.768 kHz operation)

Fig. 5-6 Clock Output Control Block Diagram

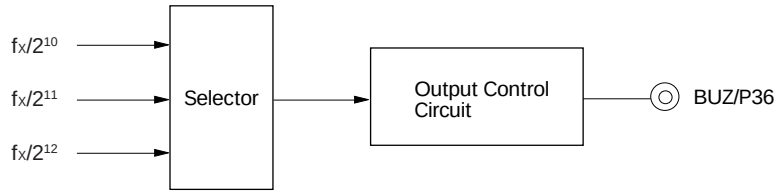


5.5 BUZZER OUTPUT CONTROL CIRCUIT

The clock with the following frequencies can be output for buzzer output.

- 2.4 kHz/4.9 kHz/9.8 kHz (Main system clock: at 10.0 MHz operation)

Fig. 5-7 Buzzer Output Control Block Diagram

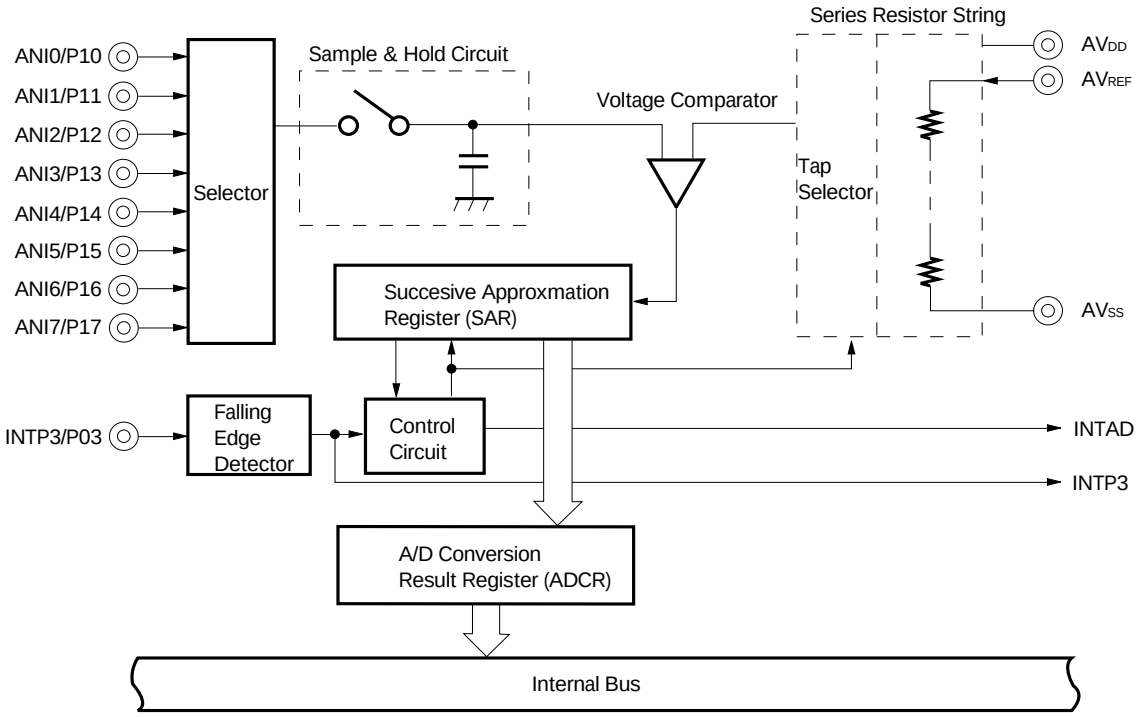


5.6 A/D CONVERTER

The A/D converter has on-chip eight 8-bit resolution channels.
There are the following two method to start A/D conversion.

- Hardware starting
- Software starting

Fig. 5-8 A/D Converter Block Diagram



5.7 SERIAL INTERFACES

There are two on-chip clocked serial interfaces as follows.

- Serial Interface channel 0
- Serial Interface channel 1

Table 5-3 Type and Function of Serial Interface

Function	Serial Interface Channel 0	Serial Interface Channel 1
3-wire serial I/O mode	○ (MSB/LSB-first switchable)	○ (MSB/LSB-first switchable)
3-wire serial I/O mode with automatic data transmit /receive function	–	○ (MSB/LSB-first switchable)
SBI (Serial Bus Interface) mode	○ (MSB-first)	–
2-wire serial I/O mode○ (MSB-first)	–	–

Fig. 5-9 Serial Interface Channel 0 Block Diagram

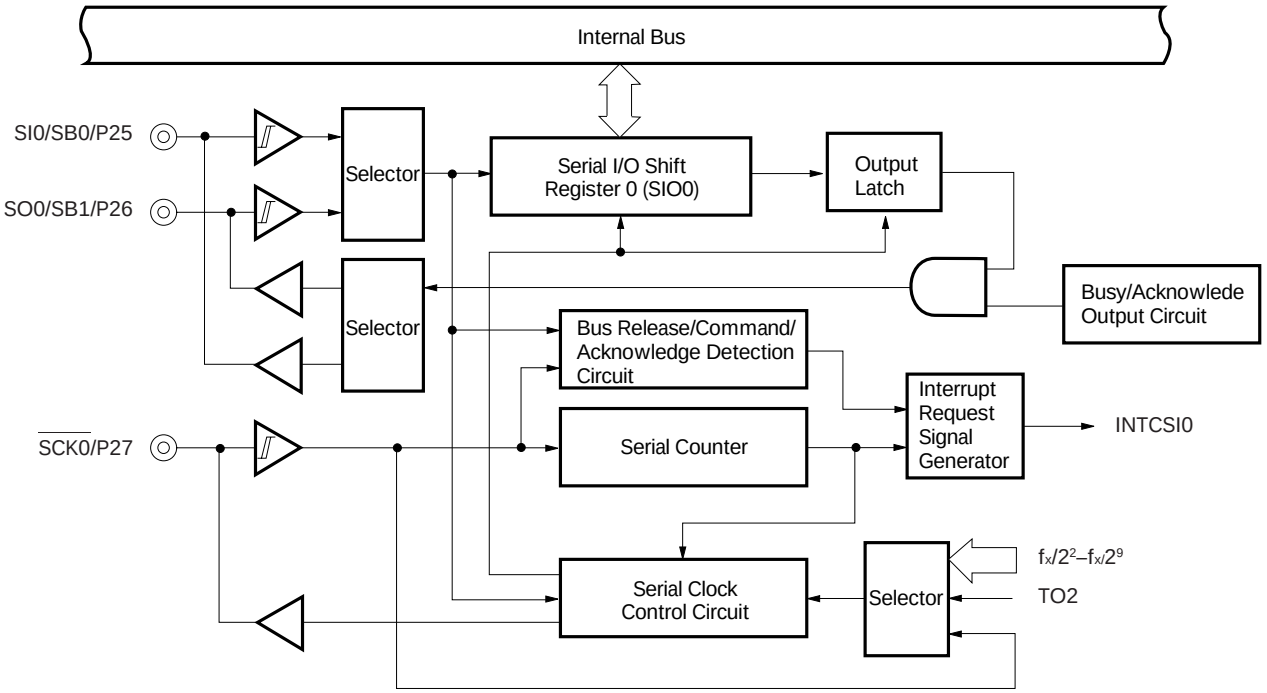
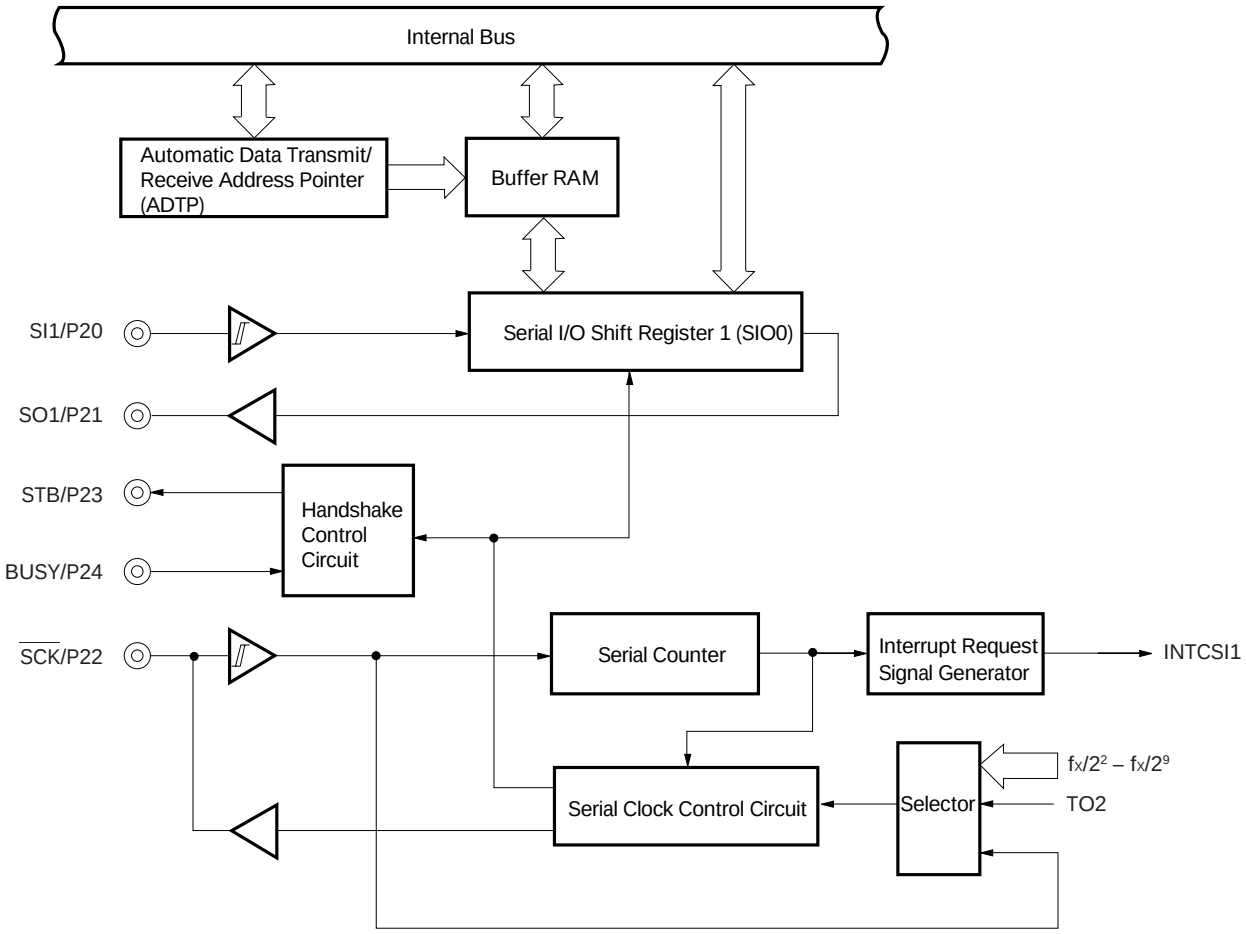


Fig. 5-10 Serial Interface Channel 1 Block Diagram



6. INTERRUPT FUNCTIONS AND TEST FUNCTIONS

6.1 INTERRUPT FUNCTIONS

There are the 14 interrupt functions of 3 different kind as shown below.

- Non-maskable interrupt : 1
- Maskable interrupt : 12
- Software interrupt : 1

Table 6-1 Interrupt Source List

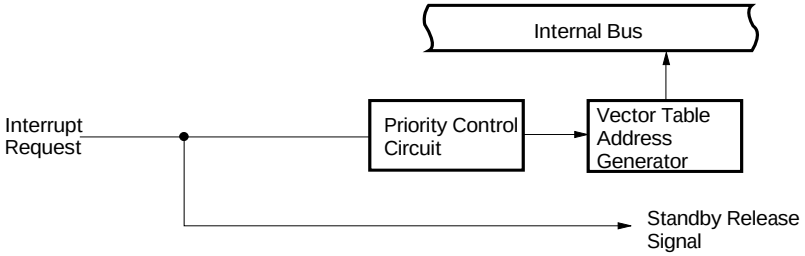
Interrupt Type	Default Priority*1	Interrupt Source		Internal /External	Vector Table Address	Basic*2 Configuratin Type
		Name	Trigger			
Non-maskable	—	INTWDT	Watchdog timer overflow (with non-maskable interrupt selected)	Internal	0004H	A
Maskable	0	INTWDT	Watchdog timer overflow (with interval timer selected)			B
	1	INTP0	Pin input edge detection	External	0006H	C
	2	INTP1			0008H	D
	3	INTP2			000AH	
	4	INTP3			000CH	
	5	INTCSI0	Serial interface channel 0 transfer end	Internal	000EH	B
	6	INTCSI1	Serial interface channel 1 transfer end		0010H	
	7	INTTM3	Reference time interval signal from watch timer		0012H	
	8	INTTM0	16 bit timer/event counter match signal generation		0014H	
	9	INTTM1	8-bit timer/event counter 1 match signal generation		0016H	
	10	INTTM2	8-bit timer/event counter 2 match signal generation		0018H	
	11	INTAD	A/D converter conversion end		001AH	
Software	—	BRK	BRK instruction execution	Internal	003EH	E

* **1.** The default pririty is the priority applicable when more than one maskable interrupt is generated. 0 is the highest priority and 11, the lowest.

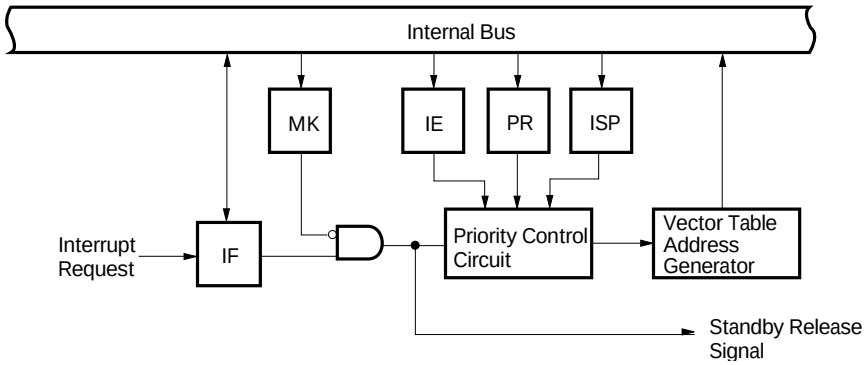
2. Basic configuration types A to E correspond to A to E on the next page.

Fig. 6-1 Basic Interrupt Function Configuration (1/2)

(A) Internal Non-Maskable Interrupt



(B) Internal Maskable Interrupt



(C) External Maskable Interrupt (INTP0)

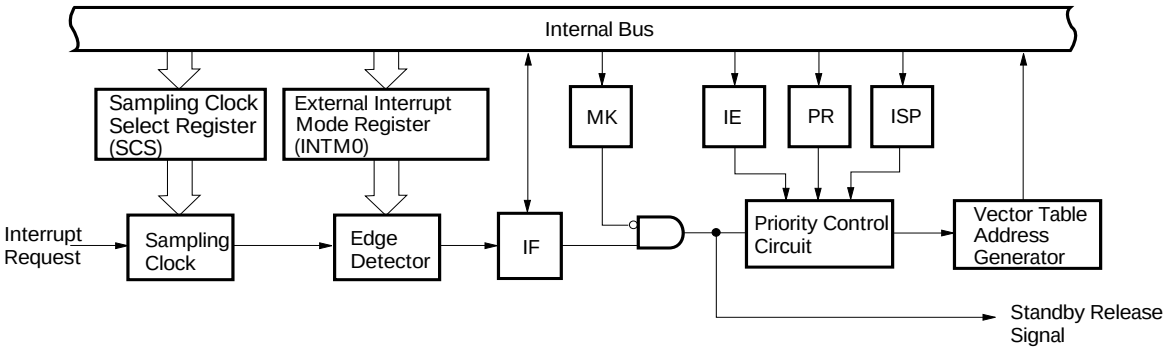
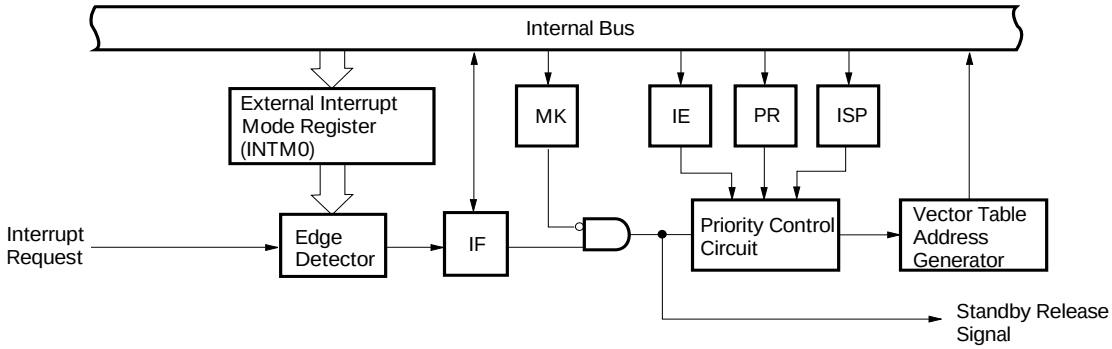
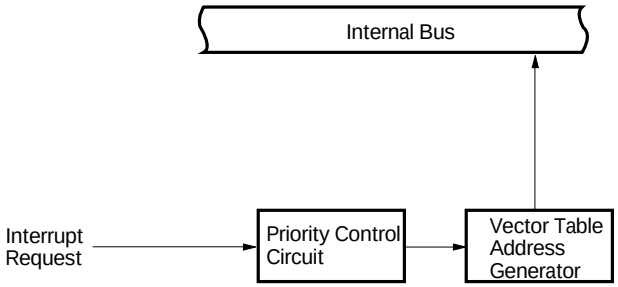


Fig. 6-1 Basic Interrupt Function Configuration (2/2)

(D) External Maskable Interrupt (Except INTP0)



(E) Software Interrupt



Remarks
1. IF : Interrupt request flag
2. IE : Interrupt enable flag
3. ISP : In-service priority flag
4. MK : Interrupt mask flag
5. PR : Priority spcification flag

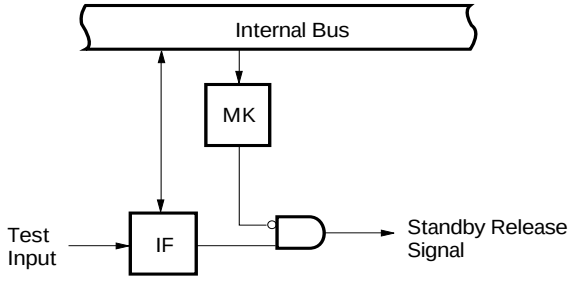
6.2 TEST FUNCTIONS

There are two test functions as shown in Table 6-2.

Table 6-2 Test Source List

Test Source		Internal/External
Name	Trigger	
INTWT	Watch timer overflow	Internal
INTPT4	Port 4 falling edge detection	External

Fig. 6-2 Test Function Basic Configuration



Remarks 1. IF : Test input flag
2. MK : Test mask flag

7. EXTERNAL DEVICE EXPANSION FUNCTIONS

The external device expansion function is used to connect external devices to areas other than the internal ROM, RAM and SFR.

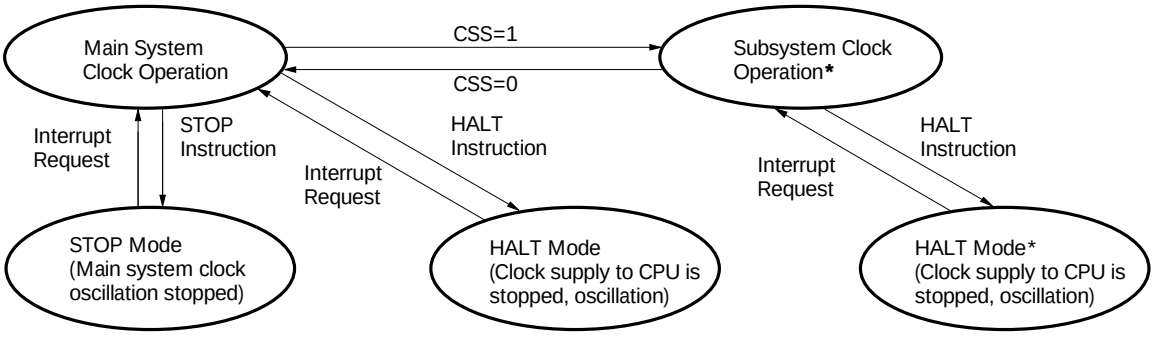
Ports 4 to 6 are used for connection with external devices.

8. STANDBY FUNCTIONS

There are the following two standby functions to reduce the current dissipation.

- HALT mode : The CPU operating clock is stopped. The average consumption current can be reduced by intermittent operation in combination with the normal operat ing mode.
- STOP mode : The main system clock oscillation is stopped. The whole operation by the main system clock is stopped, so that the system operates withultra-low power consumption using only the subsystem clock.

Fig. 8-1 Standby Functions



***** The power consumption can be reduced by stopping the main system clock. When the CPU is operating on the subsystem clock, set the MCC to stop the main system clock. The STOP instruction cannot be used.

Caution When the main system clock is stopped and the system is operated by the subsystem clock, the subsystem clock should be switched again to the main system clock after the oscillation stabilization time is secured by the program by the program.

9. RESET FUNCTIONS

There are the following two reset methods.

- External reset input by $\overline{\text{RESET}}$ pin.
- Internal reset by watchdog timer runaway time detection.

10. INSTRUCTION SET

(1) 8-Bit Instruction

MOV, XCH, ADD, ADDC, SUB, SUBC, AND, OR, XOR, CMP, MULU, DIVUW, INC, DEC, ROR, ROL, RORC, ROLC, ROR4, ROL4, PUSH, POP, DBNZ

2nd Operand / 1st Operand	#byte	A	r*	sfr	saddr	!addr16	PSW	[DE]	[HL]	[HL+byte] [HL+B] [HL+C]	$adder16	1	None
A	ADD ADDC SUB SUBC AND OR XOR CMP		MOV XCH ADD ADDC SUB SUBC AND OR XOR CMP	MOV XCH	MOV XCH ADD ADDC SUB SUBC AND OR XOR CMP	MOV XCH ADD ADDC SUB SUBC AND OR XOR CMP	MOV	MOV XCH	MOV XCH ADD ADDC SUB SUBC AND OR XOR CMP	MOV XCH ADD ADDC SUB SUBC AND OR XOR CMP		ROR ROL RORC ROLC	
r	MOV	MOV ADD ADDC SUB SUBC AND OR XOR CMP											INC DEC
r1											DBNZ		
sfr	MOV	MOV											
sadder	MOV ADD ADDC SUB SUBC AND OR XOR CMP	MOV									DBNZ		INC DEC
!adder16		MOV											
PSW	MOV	MOV											PUSH POP
[DE]		MOV											
[HL]		MOV											ROR4 ROL4
[HL+byte] [HL+B] [HL+C]		MOV											
X													MULU
C													DIVUW

* Except r=A

(2) 16-Bit Instruction

MOVW, XCHW ADDW, SUBW, CMPW, PUSH, POP, INCW, DECW

1st Operand \ 2nd Operand	#byte	AX	rp*	sfrp	saddrp	!addr16	SP	None
AX	ADDW SUBW CMPW		MOVW XCHW	MOVW	MOVW	MOVW	MOVW	
rp	MOVW	MOVW*						INCW, DECW PUSH, POP
sfrp	MOVW	MOVW						
sadderp	MOVW	MOVW						
!adder16		MOVW						
SP	MOVW	MOVW						

* Only when rp=BC, DE, HL.

(3) Bit Manipulation Instruction

MOV1, AND1, OR1, XOR1, SET1, CLR1, NOT1, BT, BF, BTCLR

1st Operand \ 2nd Operand	A.bit	sfr.bit	saddr.bit	PWS.bit	[HL].bit	CY	$addr16	None
A.bit						MOV1	BT BF BTCLR	SET1 CLR1
sfr.bit						MOV1	BT BF BTCLR	SET1 CLR1
saddr.bit						MOV1	BT BF BTCLR	SET1 CLR1
PSW.bit						MOV1	BT BF BTCLR	SET1 CLR1
[HL].bit						MOV1	BT BF BTCLR	SET1 CLR1
CY	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1			SET1 CLR1 NOT1

(4) Call Instruction/Branch Instruction

CALL, CALLF, CALLT, BR, BC, BNC, BZ, BNZ, BT, BF, BTCLR, DBNZ

2nd Operand / 1st Operand	AX	!addr16	!addr11	[addr5]	$addr16
Basic instruction	BR	CALL, BR	CALLF	CALLT	BR, BC, BNC, BZ, BNZ
Compound instruction					BT, BF, BTCLR, DBNZ

(5) Other Instruction

ADJBA, ADJBS, BRK, RET, RETI, RETB, SEL, NOP, EI, DI, HALT, STOP

11. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Test Conditions		Rating	Unit
Supply voltage	V_{DD}			–0.3 to + 7.0	V
	AV_{DD}			–0.3 to V_{DD} + 0.3	V
	AV_{REF}			–0.3 to V_{DD} + 0.3	V
	AV_{SS}			–0.3 to + 0.3	V
Input voltage	V_{I1}	P00 to P04, P10 to P17, P20 to P27, P30 toP37 P40 toP47, P50 to P57, P64 to P67, X1, X2, XT2		–0.3 to V_{DD} + 0.3	V
	V_{I2}	P60 to P67	Open-drain	–0.3 to +16	V
Output voltage	V_O			–0.3 to V_{DD} + 0.3	V
Analog input voltage	V_{AN}	P10 to P17	Analog input pin	AV_{SS} –0.3 to AV_{REF} + 0.3	V
Output current high	I_{OH}	1 pin		–10	mA
		P10 to P17, P20 to P27, P30 to P37 total		–15	mA
		P01 to P03, P40 to P47, P50 to P57, P60 to P67 total		–15	mA
Output current low	I_{OL}*	1 pin	Peak value	30	mA
			Effective value	15	mA
		P40 to P47, P50 to P55 total	Peak value	100	mA
			Effective value	70	mA
		P01 to P03, P56, P57, P60 to P67 total	Peak value	100	mA
			Effective value	70	mA
		P01 to P03, P64 to P67 total	Peak value	50	mA
			Effective value	20	mA
		P10 to P17, P20 to P27, P30 to P37 total	Peak value	50	mA
			Effective value	20	mA
Operating temperature	T_{opt}			–40 to +85	°C
Storage temperature	T_{stg}			–65 to +150	°C

* Effective value should be calculated as follows: [Effective value] = [Peak value] × $\sqrt{\text{duty}}$

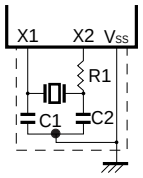
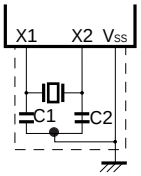
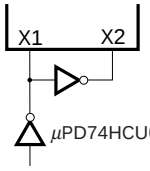
Caution Product quality may suffer if the absolute maximum rating is exceeded for even a single parameter or even momentarily. That is, the absolute maximuam ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions which ensure that the absolute maximum ratings are not exceeded.

Capacitance (Ta = 25 °C, V_{DD} = V_{SS} = 0 V)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
Input capacitance	C_{IN}	f=1 MHz Unmeasured pins returned to 0 V				15	pF
I/O capacitance	C_{IO}	f=1 MHz Unmeasured pins returned to 0 V	P01 to P03, P10 to P17, P20 to P27, P30 toP37, P40 toP47, P50 to P57, P64 to P67			15	pF
			P60 to P63			20	pF

Remarks The characteristics of a dual-function pin and a port pin are the same unless specified otherwise.

Main System Clock Oscillation Circuit Characteristics (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Resonator	Recommended Circuit	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator		Oscillator frequency (fx) ***1**	V_{DD} = Oscillator voltage range	1		10	MHz
		Oscillation stabilization time ***2**	After V_{DD} reaches oscillator voltage range MIN.			4	ms
Crystal resonator		Oscillator frequency (fx) ***1**		1	8.38	10	MHz
		Oscillation stabilization time ***2**	V_{DD} = 4.5 to 6.0 V			10	ms
						30	
External clock		X1 input frequency (fx) ***1**		1.0		10.0	MHz
		X1 input high/low level width (t_{XH}, t_{XL})		42.5		500	ns

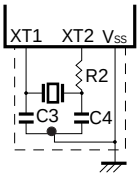
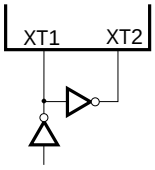
*** 1.** Indicates only oscillation circuit characteristics. Refer to “AC Characteristics” for instruction execution time.
2. Time required to stabilize oscillation after reset or STOP mode release.

Caution 1. When using the main system clock oscillator, wirinin the area enclosed with the dotted line should be carried out as follows to avoid an adverse effect from wiring capacitance.

- **Wiring should be as short as possible.**
- **Wiring should not cross other signal lines.**
- **Wiring should not be placed close to a varying high current.**
- **The potential of the oscillator capacitor groundshould be the same as V_{SS}.**
- **Do not ground wiring to a ground pattern in which a high current flows.**
- **Do not fetch a signal from the oscillator.**

2. When the main system clock is stopped and the system is operated by the subsystem clock, the subsystem clock should be switched again to the main system clock after the oscillation stabilization time is secured by the program.

Subsystem Clock Oscillation Circuit Characteristics (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Resonator	Recommended Circuit	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Crystal resonator		Oscillator frequency (f_{XT}) ***1**		32	32.768	35	kHz
		Oscillation stabilization time ***2**	V_{DD} = 4.5 to 6.0 V		1.2	2	s
						10	
External clock		XT1 input frequency (f_{XT}) ***1**		32		100	kHz
		XT1 input high/low level width (t_{XTH}, t_{XTL})		5		15	μs

***** **1.** Indicates only oscillation circuit characteristics. Refer to "AC Characteristics" for instruction execution time.
2. Time required to stabilize oscillation after V_{DD} reaches oscillator voltage MIN.

Caution 1. When using the subsystem clock oscillator, wiring in the area enclosed with the dotted line should be carried out as follows to avoid an adverse effect from wiring capacitance.

- **Wiring should be as short as possible.**
- **Wiring should not cross other signal lines.**
- **Wiring should not be placed close to a varying high current.**
- **The potential of the oscillator capacitor ground should be the same as V_{SS}.**
- **Do not ground wiring to a ground pattern in which a high current flows.**
- **Do not fetch a signal from the oscillator.**

2. The subsystem clock oscillation circuit is a circuit with a low amplification level,more prone to misoperation due to noise than the main system clock.
Particular care is therefore required with the wiring method when the subsystem clock is used.

Recommended Oscillation Circuit Constant

Main system clock: Ceramic resonator (Ta = –40 to +85 °C)

μPD78011B, 78012B

Manufacture	Product Name	Frequency (MHz)	Recommended Circuit Constant			Oscillator Voltage Range	
			C1 (pF)	C2 (pF)	R1 (kΩ)	MIN. (V)	MAX. (V)
Murata Mfg. Co., Ltd.	CSB1000J	1.00	100	100	6.8	2.9	6.0
	CSB××××J	1.01 to 1.25	100	100	4.7	2.7	6.0
	CSA×. ×××MK	1.26 to 1.79	100	100	0	2.7	6.0
	CSA×. ××MG	1.80 to 2.44	100	100	0	2.7	6.0
	CST×. ××MG		Built-in	Built-in	0	2.7	6.0
	CSA×. ××MG	2.45 to 4.18	30	30	0	2.7	6.0
	CST×. ××MGW		Built-in	Built-in	0	2.7	6.0
	CSA×. ××MG	4.19 to 6.00	30	30	0	2.7	6.0
	CST×. ××MGW		Built-in	Built-in	0	2.7	6.0
	CSA×. ××MT	6.01 to 10.0	30	30	0	2.9	6.0
	CST×. ××MTW		Built-in	Built-in	0	2.9	6.0
Kyocera	KBR-4.19MWS	4.19	–	–	–	2.7	6.0
	KBR-4.19MKS						
	KBR-4.19MSA	4.19	33	33	–	2.7	6.0
	PBRC4.19A						
	KBR-10.0M	10.0	33	33	–	2.8	6.0
	KBR-1000F	1.00	100	100	2.2	2.7	6.0
	KBR-1000Y						

μPD78013, 78014

Manufacture	Product Name	Frequency (MHz)	Recommended Circuit Constant			Oscillator Voltage Range	
			C1 (pF)	C2 (pF)	R1 (kΩ)	MIN. (V)	MAX. (V)
Murata Mfg. Co., Ltd.	CSB1000J	1.00	100	100	6.8	2.7	6.0
	CSB××××J	1.01 to 1.25	100	100	4.7	2.7	6.0
	CSA×. ×××MK	1.26 to 1.79	100	100	0	2.7	6.0
	CSA×. ××MG	1.80 to 2.44	100	100	0	2.7	6.0
	CST×. ××MG		Built-in	Built-in	0	2.7	6.0
	CSA×. ××MG	2.45 to 4.18	30	30	0	2.7	6.0
	CST×. ××MGW		Built-in	Built-in	0	2.7	6.0
	CSA×. ××MG	4.19 to 6.00	30	30	0	2.7	6.0
	CST×. ××MGW		Built-in	Built-in	0	2.7	6.0
	CSA×. ××MT	6.01 to 10.0	30	30	0	2.7	6.0
	CST×. ××MTW		Built-in	Built-in	0	2.7	6.0

Remarks ××××, ×. ×××, ×. ×× indicate frequency.

Subsystem clock: Cristal resonator (Ta = –40 to + 60 °C)

μPD78011B, 78012B

Manufacture	Products	Frequency (MHz)	Recommended Circuit Constant			Oscillator Voltage Range	
			C3 (pF)	C4 (pF)	R2 (kΩ)	MIN. (V)	MAX. (V)
Daishinku	DT-38 (1TA632 E00, load capacitance 6.3 pF)	32.768	8	8	100	2.7	6.0

μPD78013, 78014

Manufacture	Product Name	Frequency (MHz)	Recommended Circuit Constant			Oscillator Voltage Range	
			C3 (pF)	C4 (pF)	R2 (kΩ)	MIN. (V)	MAX. (V)
Daishinku	DT-38 (1TA632 E00, load capacitance 6.3 pF)	32.768	12	12	100	2.7	6.0

DC Characteristics (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
Input voltage high	V_{IH1}	P10 to P17, P21, P23, P30 to P32, P35 to P37, P40 to P47, P50 to P57, P64 to P67		0.7 V_{DD}		V_{DD}	V
	V_{IH2}	P00 to P03, P20, P22, P24 to P27, P33, P34, $\overline{RESET}$		0.8 V_{DD}		V_{DD}	V
	V_{IH3}	P60 to P63	Open-drain	0.7 V_{DD}		15	V
	V_{IH4}	X1, X2		V_{DD}-0.5		V_{DD}	V
	V_{IH5}	XT1/P04, XT2	V_{DD} = 4.5 to 6.0 V	V_{DD}-0.5		V_{DD}	V
				V_{DD}-0.3		V_{DD}	V
Input voltage low	V_{IL1}	P10 to P17, P21, P23, P30 to P32, P35 to P37 P40 to P47, P50 to P57, P64 to P67		0		0.3 V_{DD}	V
	V_{IL2}	P00 to P03, P20, P22, P24 to P27, P33, P34, $\overline{RESET}$		0		0.2 V_{DD}	V
	V_{IL3}	P60 to P63	V_{DD} = 4.5 to 6.0 V	0		0.3 V_{DD}	V
				0		0.2 V_{DD}	V
	V_{IL4}	X1, X2		0		0.4	V
	V_{IL5}	XT1/P04, XT2	V_{DD} = 4.5 to 6.0 V	0		0.4	V
				0		0.3	V
Output voltage high	V_{OH1}	V_{DD} = 4.5 to 6.0 V, I_{OH} = –1 mA		V_{DD}-1.0			V
		I_{OH} = –100 μA		V_{DD}-0.5			V
Output voltage low	V_{OL1}	P50 to P57, P60 to P63	V_{DD} = 4.5 to 6.0 V, I_{OL} = 15 mA		0.4	2.0	V
		P01 to P03, P10 to P17, P20 to P27 P30 to P37, P40 to P47, P64 to P67	V_{DD} = 4.5 to 6.0 V, I_{OL} = 1.6 mA			0.4	V
	V_{OL2}	SB0, SB1, $\overline{SCK0}$	V_{DD} = 4.5 to 6.0 V, open-drain pulled-up (R = 1 KΩ)			0.2 V_{DD}	V
	V_{OL3}	I_{OL} = 400 μA				0.5	V
Input leakage current high	I_{LIH1}	V_{IN} = V_{DD}	P00 to P03, P10 to P17, P20 to P27, P30 to P37, P40 to P47, P50 to P57, P60 to P67 $\overline{RESET}$			3	μA
	I_{LIH2}		X1, X2, XT1/P04, XT2			20	μA
	I_{LIH3}	V_{IN} = 15 V	P60 to P63			80	μA
Input leakage current low	I_{LIL1}	V_{IN} = 0 V	P00 to P03, P10 to P17, P20 to P27, P30 to P37, P40 to P47, P50 to P57, P64 to P67 $\overline{RESET}$			–3	μA
	I_{LIL2}		X1, X2, XT1/P04, XT2			–20	μA
	I_{LIL3}		P60 to P63 ***1**			–200	μA
			Other than above			–3***2**	μA

*** 1.** When memory expansion mode is used by the memory expansion mode register (MM) with no on-chip pull-up resistor by mask option.

2. When pull-up resistors are not used (specified by mask option), the low-level input leakage current increases with –200 μA (MAX.) under either of the following conditions.

① When the external device expansion function is used and a low level is input to the pin.
② During the 3-clock period when a read instruction is executed on port 6 (P6) and the port mode registor (PM6).

Remarks The characteristics of a dual-function pin and a port pin are the same unless specified otherwise.

DC Characteristics (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
Output leakage current high	I_{LOH1}	$V_{OUT} = V_{DD}$				3	μA
Output leakage current low	I_{LOL}	V_{OUT} = 0 V				–3	μA
Mask option pull-up resister	R1	V_{IN} = 0 V, P60 to P63		20	40	90	kΩ
Software pull-up resister	R2	V_{IN} = 0 V, P01 to P03, P10 to P17, P20 to P27, P30 to P37, P40 to P47, P50 to P57, P60 to P67	4.5 V ≤ V_{DD} ≤ 6.0 V	15	40	90	kΩ
			2.7 V ≤ V_{DD} < 4.5 V	20		500	kΩ
Power supply current ***5**	I_{DD1}	8.38 MHz Crystal oscillation operating mode	V_{DD} = 5.0 V ± 10 % ***3**		7.5	22.5	mA
			V_{DD} = 3.0 V ± 10 % ***4**		0.8	2.4	mA
	I_{DD2}	8.38 MHz Crystal oscillation HALT mode	V_{DD} = 5.0 V ± 10 %		1.4	4.2	mA
			V_{DD} = 3.0 V ± 10 %		550	1650	μA
	I_{DD3}	32.768 kHz Crystal oscillation operating mode	V_{DD} = 5.0 V ± 10 %		60	120	μA
			V_{DD} = 3.0 V ± 10 %		35	70	μA
	I_{DD4}	32.768 kHz Crystal oscillation HALT mode	V_{DD} = 5.0 V ± 10 %		25	50	μA
			V_{DD} = 3.0 V ± 10 %		5	10	μA
	I_{DD5}	XT1 = 0 V STOP mode When feedback resister is used	V_{DD} = 5.0 V ± 10 %		1	20	μA
			V_{DD} = 3.0 V ± 10 %		0.5	10	μA
	I_{DD6}	XT1 = 0 V STOP mode When feedback resister is unused	V_{DD} = 5.0 V ± 10 %		0.1	20	μA
			V_{DD} = 3.0 V ± 10 %		0.05	10	μA

*** 3.** Operating in high-speed mode (when set the processor clock control register to 00H).

4. Operating in low-speed mode (when set the processor clock control register to 04H).

5. AV_{REF} current and port current are excluded.

Remarks The characteristics of a dual-function pin and a port pin are the same unless specified otherwise.

AC Characteristics

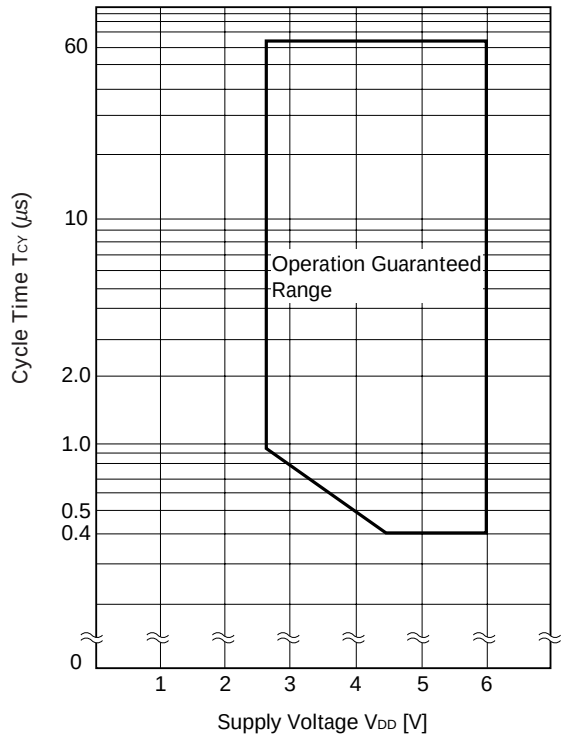
(1) Basic Operation (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
Cycle time (Min. instruction execution time)	T_{CY}	Operating on main system clock	V_{DD}=4.5 to 6.0 V	0.4		64	μs
				0.96		64	μs
		Operationg on subsystem clock		40	122	125	μs
TI input frequency	f_{TI}	V_{DD} = 4.5 to 6.0 V		0		4	MHz
				0		275	kHz
TI input high/ low-level width	t_{TIH}	V_{DD} = 4.5 to 6.0 V		100			ns
	t_{TIL}			1.8			μs
Interrupt input high/low-level width	t_{INTH}	INTP0		8/f_{sam}*			μs
	t_{INTL}	INTP1 to INTP3		10			μs
		KR0 to KR7		10			μs
$\overline{\text{RESET}}$ low level width	t_{RSL}			10			μs

***** In combination with bits 0 (SCS0) and 1 (SCS1) of sampling clock select register, selection of f_{sam} is possible between $f_X/2^{N+1}$, $f_X/64$ and $f_X/128$ (when N= 0 to 4).

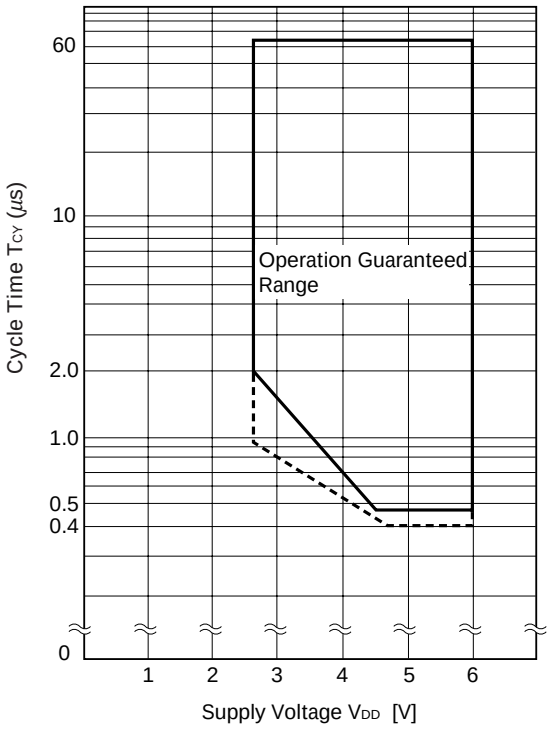
μPD78011B, 78012B, 78013, 78014

T_{CY} vs V_{DD} (At main system clock operation)



μPD78P014 (Reference)

T_{CY} vs V_{DD} (At main system clock operation)



Remarks ------- indicates Ta=–40 to +40 °C
——— indicates Ta=–40 to +80 °C

Caution The operation guaranteed range of the μPD78011B, 78012B, 78013 and 78014 differs from that of the μPD78P014.

(2) Read/Write Operation (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Parameter	Symbol	Test Conditions	MIN.	MAX.	Unit
ASTB high-level width	t_{ASTH}		$0.5t_{CY}$		ns
Address setup time	t_{ADS}		$0.5t_{CY}$–30		ns
Address hold time	t_{ADH}	Load resistor ≥ 5 kΩ	10		ns
Data input time from address	t_{ADD1}			$(2+2n)t_{CY}$–50	ns
	t_{ADD2}		5	$(3+2n)t_{CY}$–100	ns
Data input time from $\overline{RD}\downarrow$	t_{RDD1}			$(1+2n)t_{CY}$–25	ns
	t_{RDD2}			$(2.5+2n)t_{CY}$–100	ns
Read data hold time	t_{RDH}		0		ns
$\overline{RD}$ low-level width	t_{RDL1}		$(1.5+2n)t_{CY}$–20		ns
	t_{RDL2}		$(2.5+2n)t_{CY}$–20		ns
$\overline{WAIT}\downarrow$ input time from $\overline{RD}\downarrow$	t_{RDWT1}			$0.5t_{CY}$	ns
	t_{RDWT2}			$1.5t_{CY}$	ns
$\overline{WAIT}\downarrow$ input time from $\overline{WR}\downarrow$	t_{WRWT}			$0.5t_{CY}$	ns
$\overline{WAIT}$ low-level width	t_{WTL}		$(0.5+2n)t_{CY}$ +10	$(2+2n)t_{CY}$	ns
Write data setup time	t_{WDS}		100		ns
Write data hold time	t_{WDH}		5		ns
$\overline{WR}$ low-level width	t_{WRL1}		$(2.5+2n)t_{CY}$ –20		ns
$\overline{RD}\downarrow$ delay time from ASTB↓	t_{ASTRD}		$0.5t_{CY}$–30		ns
$\overline{WR}\downarrow$ delay time from ASTB↓	t_{ASTWR}		$1.5t_{CY}$ –30		ns
ASTB↑ delay time from $\overline{RD}\uparrow$ in external fetch	t_{RDAST}		t_{CY}-10	t_{CY}+40	ns
Address hold time from $\overline{RD}\uparrow$ in external fetch	t_{RDADH}		t_{CY}	t_{CY}+50	ns
Write data output time from $\overline{RD}\uparrow$	t_{RDWD}		10		ns
$\overline{WR}\downarrow$ delay time from write data	t_{WDWR}	V_{DD} = 4.5 to 6.0 V	$0.5t_{CY}$–120	$0.5t_{CY}$	ns
			$0.5t_{CY}$–170	$0.5t_{CY}$	ns
Address hold time from $\overline{WR}\uparrow$	t_{WRADH}	V_{DD} =4.5 to 6.0 V	t_{CY}	t_{CY}+60	ns
			t_{CY}	t_{CY}+100	ns
$\overline{RD}\uparrow$ delay time from $\overline{WAIT}\uparrow$	t_{WTRD}		$0.5t_{CY}$	$2.5t_{CY}$+80	ns
$\overline{WR}\uparrow$ delay time from $\overline{WAIT}\uparrow$	t_{WTWR}		$0.5t_{CY}$	$2.5t_{CY}$+80	ns

Remarks **1.** $t_{CY} = T_{CY}/4$

2. n indicates number of waits.

3. C_L = 100 pF (C_L indicates load capacitance of P40/AD0 to P47/AD7, P50/A8 to P57/A15, P64/ $\overline{RD}$, P65/$\overline{WR}$, P66/$\overline{WAIT}$,P67/ASTB pins).

(3) Serial Interface (Ta = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

(a) 3-wire serial I/O mode ($\overline{SCK}$... Internal clock output)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
$\overline{SCK}$ cycle time	t_{KCY1}	V_{DD} = 4.5 to 6.0 V		800			ns
				3200			ns
$\overline{SCK}$ high/low-level width	t_{KH1}	V_{DD} = 4.5 to 6.0 V		t_{KCY1}/2-50			ns
	t_{KL1}			t_{KCY1}/2-150			ns
SI setup time (to $\overline{SCK}$↑)	t_{SIK1}			100			ns
SI hold time (from $\overline{SCK}$↑)	t_{KSI1}			400			ns
SO output delay time from $\overline{SCK}$↓	t_{KSO1}	C = 100 pF*	V_{DD} = 4.5 to 6.0 V			300	ns
						1000	ns

* C is the load capacitance of SO output line.

(b) 3-wire serial I/O mode ($\overline{SCK}$... External clock input)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
$\overline{SCK}$ cycle time	t_{KCY2}	V_{DD} = 4.5 to 6.0 V		800			ns
				3200			ns
$\overline{SCK}$ high/low-level width	t_{KH2}	V_{DD} = 4.5 to 6.0 V		400			ns
	t_{KL2}			1600			ns
SI setup time (to $\overline{SCK}$↑)	t_{SIK2}			100			ns
SI hold time (from $\overline{SCK}$↑)	t_{KSI2}			400			ns
SO output delay time from $\overline{SCK}$↓	t_{KSO2}	C = 100 pF*	V_{DD} = 4.5 to 6.0 V			300	ns
						1000	ns
★ $\overline{SCK}$ rise, fall time (When serial interface channel 0 is used)	t_{R2}, t_{F2}	When external device expansion function is used				160	ns
★		When external device expansion function is not used	When 16-bit timer output function is used			700	ns
★			When 16-bit timer output function is not used			1000	ns
★ $\overline{SCK}$ rise, fall time (When serial interface channel 1 is used)	t_{R2}	When external device expansion function is used				160	ns
★	t_{F2}	When external device expansion function is not used				1000	ns

* C is the load capacitance of SO output line.

(c) SBI mode ($\overline{SCK}$... Internal clock output)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
$\overline{SCK}$ cycle time	t_{KCY3}	V_{DD} = 4.5 to 6.0 V		800			ns
				3200			ns
$\overline{SCK}$ high/low-level width	t_{KH3}	V_{DD} = 4.5 to 6.0 V		t_{KCY3}/2-50			ns
	t_{KL3}			t_{KCY3}/2-150			ns
SB0, SB1 setup time (to $\overline{SCK}$↑)	t_{SIK3}	V_{DD} = 4.5 to 6.0 V		100			ns
				300			ns
SB0, SB1 hold time (from $\overline{SCK}$↑)	t_{KSI3}			t_{KCY3}/2			ns
SB0, SB1 output delay time from $\overline{SCK}$↓	t_{KSO3}	R = 1 kΩ ,	V_{DD} = 4.5 to 6.0 V	0		250	ns
		C = 100 pF*		0		1000	ns
SB0, SB1↓ from $\overline{SCK}$↑	t_{KSB}			t_{KCY3}			ns
$\overline{SCK}$↓ from SB0, SB1↓	t_{SBK}			t_{KCY3}			ns
SB0, SB1 high-level width	t_{SBH}			t_{KCY3}			ns
SB0, SB1 low-level width	t_{SBL}			t_{KCY3}			ns

***** R and C are the load resistors and load capacitance of the SB0 and SB1 output line.

(d) SBI mode (SCK... External clock output)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
SCK cycle time	t_{KCY4}	V_{DD} = 4.5 to 6.0 V		800			ns
				3200			ns
SCK high/low-level width	t_{KH4} t_{KL4}	V_{DD} = 4.5 to 6.0 V		400			ns
				1600			ns
SB0, SB1 setup time (to SCK↑)	t_{SIK4}	V_{DD} = 4.5 to 6.0 V		100			ns
				300			ns
SB0, SB1 hold time (from SCK↑)	t_{KSI4}			t_{KCY4}/2			ns
SB0, SB1 output delay time from SCK↓	t_{KSO4}	R = 1 kΩ, C = 100 pF*	V_{DD} = 4.5 to 6.0 V	0		300	ns
				0		1000	ns
SB0, SB1↓ from SCK↑	t_{KSB}			t_{KCY4}			ns
SCK↓ from SB0, SB1↓	t_{SBK}			t_{KCY4}			ns
SB0, SB1 high-level width	t_{SBH}			t_{KCY4}			ns
SB0, SB1 low-level width	t_{SBL}			t_{KCY4}			ns
★ SCK rise, fall time	t_{R4} t_{F4}	When external device expansion function is used				160	ns
★		When external device expansion function is not used	When 16-bit timer output function is used			700	ns
★			When 16-bit timer output function is not used			1000	ns

* R and C are the load resistors and load capacitance of the SB0 and SB1 output line.

(e) 2-wire serial I/O mode (SCK... Internal clock output)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
SCK cycle time	t_{KCY5}	V_{DD} = 4.5 to 6.0 V		1600			ns
				3800			ns
SCK high-level width	t_{KH5}	R = 1 kΩ, C = 100 pF*		t_{KCY5}/2-50			ns
SCK low-level width	t_{KL5}			t_{KCY5}/2-50			ns
SB0, SB1 setup time (to SCK↑)	t_{SIK5}			300			ns
SB0, SB1 hold time (from SCK↑)	t_{KSI5}			600			ns
SB0, SB1 output delay time from SCK↓	t_{KSO5}	R = 1 kΩ, C = 100 pF*	V_{DD} = 4.5 to 6.0 V	0		250	ns
				0		1000	ns

* R and C are the load resistors and load capacitance of the SCK0, SB0 and SB1 output line.

(f) 2-wire serial I/O mode ($\overline{SCK}$... External clock input)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit	
$\overline{SCK}$ cycle time	t_{KCY6}	V_{DD} = 4.5 to 6.0 V		1600			ns	
				3800			ns	
$\overline{SCK}$ high-level width	t_{KH6}			650			ns	
$\overline{SCK}$ low-level width	t_{KL6}			800			ns	
SB0, SB1 setup time (to $\overline{SCK}$↑)	t_{SIK6}			100			ns	
SB0, SB1 hold time (from $\overline{SCK}$↑)	t_{KSI6}			t_{KCY6}/2			ns	
SB0, SB1 output delay time from $\overline{SCK}$↓	t_{KSO6}	R = 1 kΩ,	V_{DD} = 4.5 to 6.0 V	0		300	ns	
		C = 100 pF*		0		1000	ns	
$\overline{SCK}$ rise, fall time	t_{R6} t_{F6}	When external device expansion function is used				160	ns	★
		When external device expansion function is not used	When 16-bit timer output function is used			700	ns	★
			When 16-bit timer output function is not used			1000	ns	★

* R and C are the load resistors and load capacitance of the $\overline{SCK0}$, SB0 and SB1 output line.

(g) 3-wire serial I/O mode with automatic transmit/receive function ($\overline{SCK}$...Internal clock output)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	UNIT
$\overline{SCK}$ cycle time	t_{KCY7}	V_{DD} = 4.5 to 6.0 V		800			ns
				3200			ns
$\overline{SCK}$ high/low-level width	t_{KH7}	V_{DD} = 4.5 to 6.0 V		t_{KCY7}/2-50			ns
	t_{KL7}			t_{KCY7}/2-150			ns
SI setup time (to $\overline{SCK}$↑)	t_{SIK7}			100			ns
SI hold time (from $\overline{SCK}$↑)	t_{KSI7}			400			ns
SO output delay time from $\overline{SCK}$↓	t_{KSO7}	C = 100 pF*	V_{DD} = 4.5 to 6.0 V			300	ns
						1000	ns
STB↑ from $\overline{SCK}$↑	t_{SBD}			400		t_{KCY7}	ns
Strobe signal high-level width	t_{SBW}			t_{KCY7}–30		t_{KCY7}+30	ns
Busy signal setup time (to busy signal detection timing)	t_{BYS}			100			ns
Busy signal hold time (from busy signal detection timing)	t_{BYH}			100			ns
$\overline{SCK}$↓ from busy inactive	t_{SPS}					$2t_{KCY7}$	ns

***** C is the load capacitance of the SO output line.

(h) 3-wire serial I/O mode with automatic transmit/receive function ($\overline{SCK}$...External clock input)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	UNIT	
$\overline{SCK}$ cycle time	t_{KCY8}	V_{DD} = 4.5 to 6.0 V		800			ns	
				3200			ns	
$\overline{SCK}$ high/low-level width	t_{KH8}	V_{DD} = 4.5 to 6.0 V		400			ns	
	t_{KL8}			1600			ns	
SI setup time (to $\overline{SCK}$↑)	t_{SIK8}			100			ns	
SI hold time (from $\overline{SCK}$↑)	t_{KSI8}			400			ns	
SO output delay time from $\overline{SCK}$↓	t_{KSO8}	C = 100 pF*	V_{DD} = 4.5 to 6.0 V			300	ns	
						1000	ns	
$\overline{SCK}$ rise, fall time	t_{R8}	When external device expansion function function is used				160	ns	★
	t_{F8}	When external device expansion function is not used				1000	ns	★

* C is the load capacitance of the SO output line.

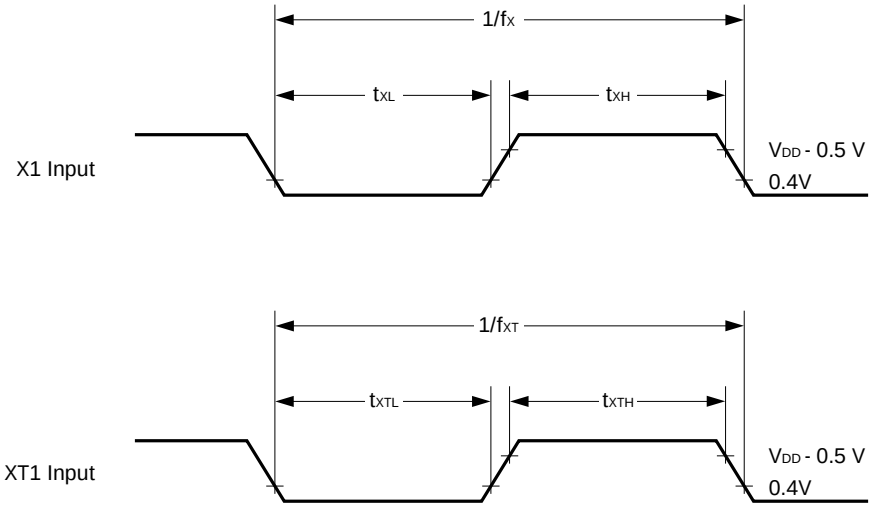
(4) A/D converter characteristics (Ta = –40 to +85 °C, $AV_{DD} = V_{DD}$ = 2.7 to 6.0 V, $AV_{SS} = V_{SS}$ = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Resolution			8	8	8	bit
Overall error*					0.6	%
Conversion time	t_{CONV}		19.1		200	μs
Sampling time	t_{SAMP}		24/fx			μs
Analog input voltage	V_{IAN}		AV_{SS}		AV_{REF}	V
Reference voltage	AV_{REF}		2.7		AV_{DD}	V
AV_{REF} current	AI_{REF}			0.5	1.5	mA

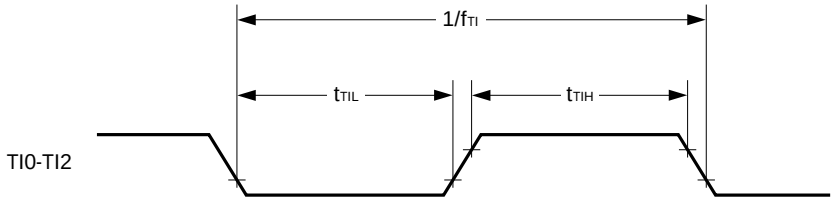
* Overroll error excluding quantization error (±1/2 LSB). It is indicated as a ratio to the full-scale value.

AC Timing Test Point (Excluding X1, XT1 Input)

Clock Timing

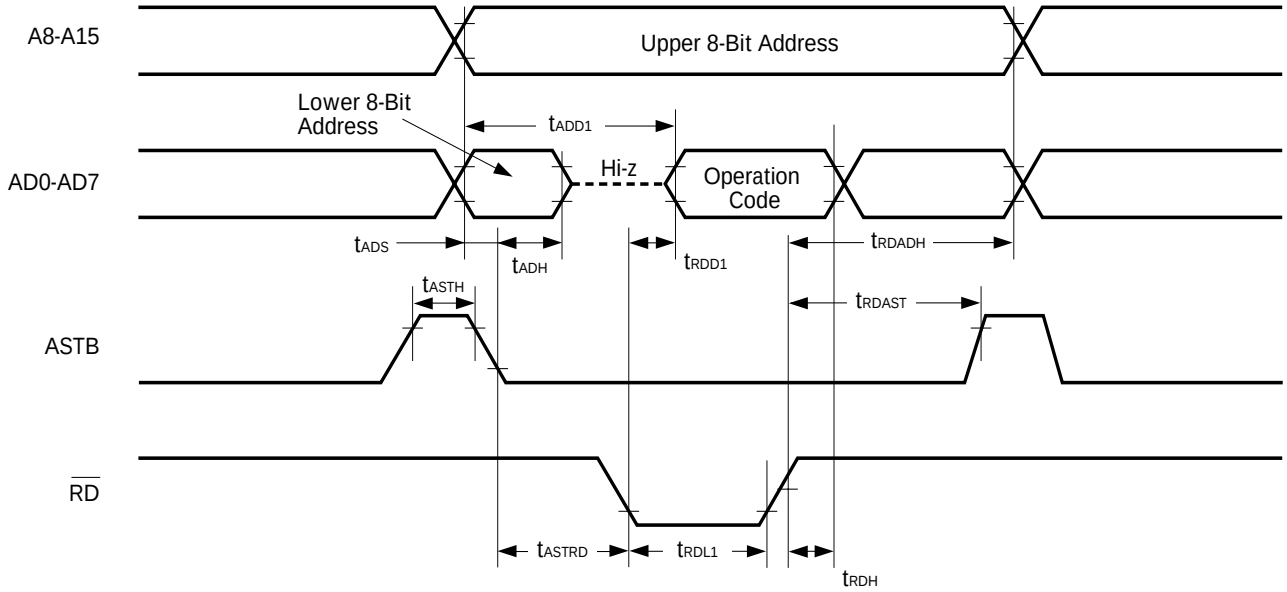


TI Timing

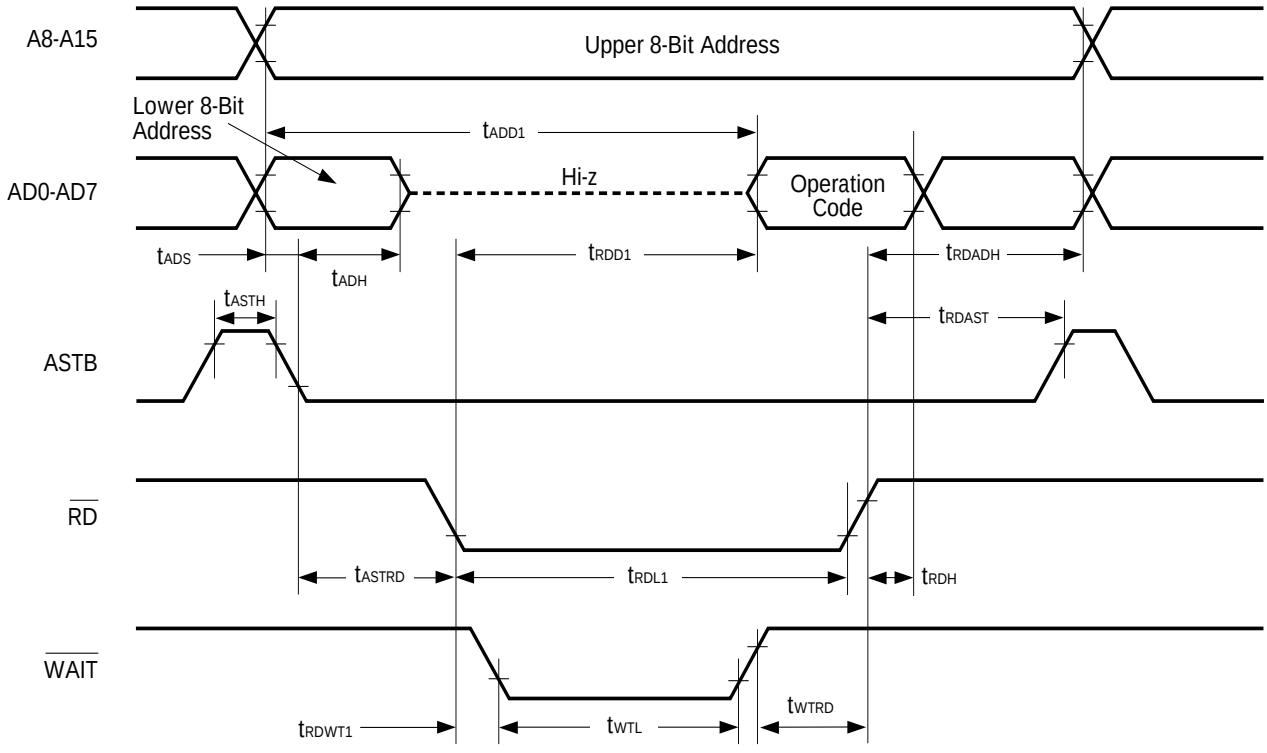


Read/Write Operation

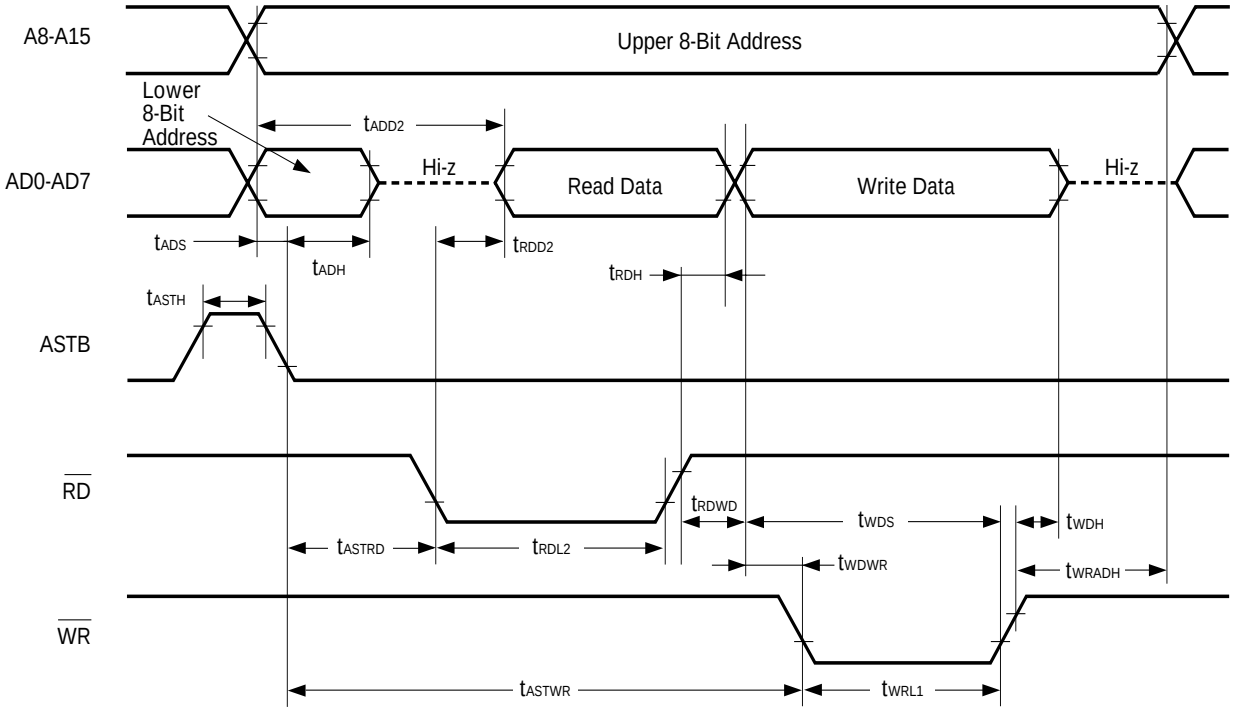
External fetch (No wait):



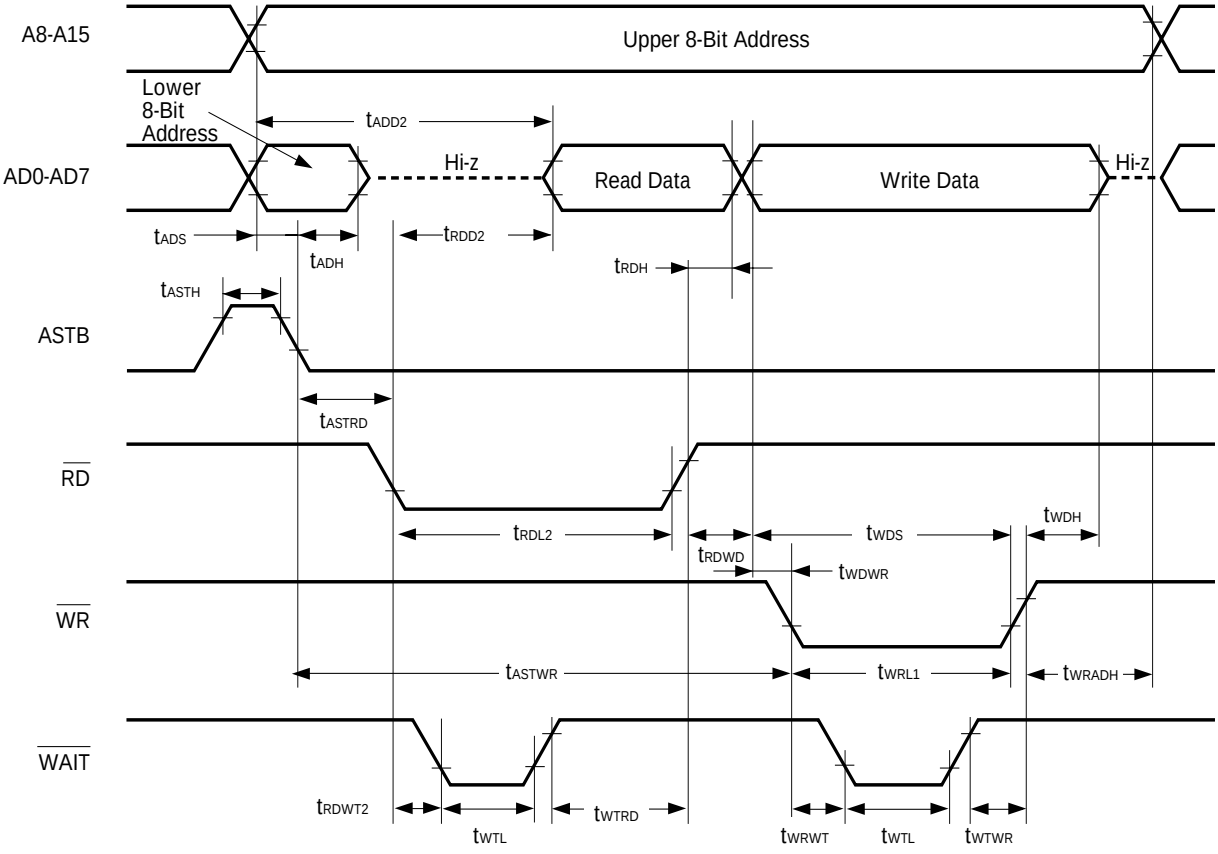
External fetch (Wait insertion):



External data access (No wait):



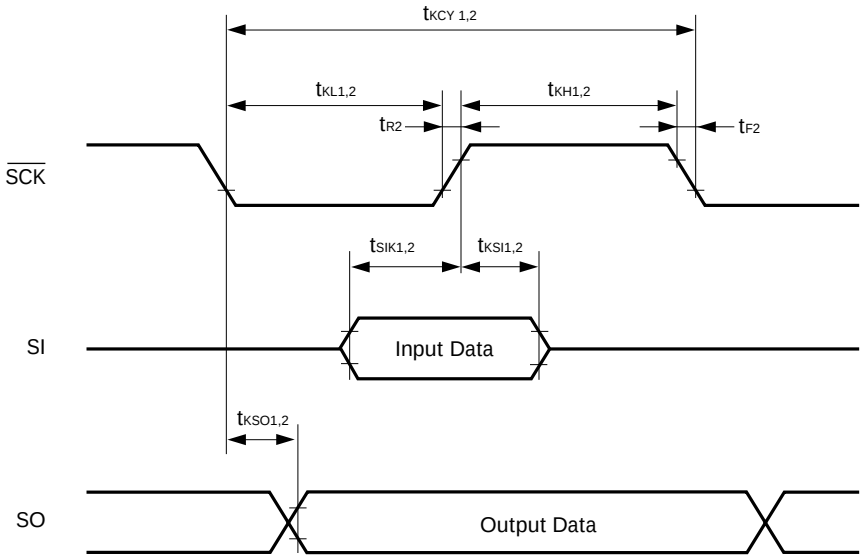
External data access (Wait insertion):



Serial Transfer Timing

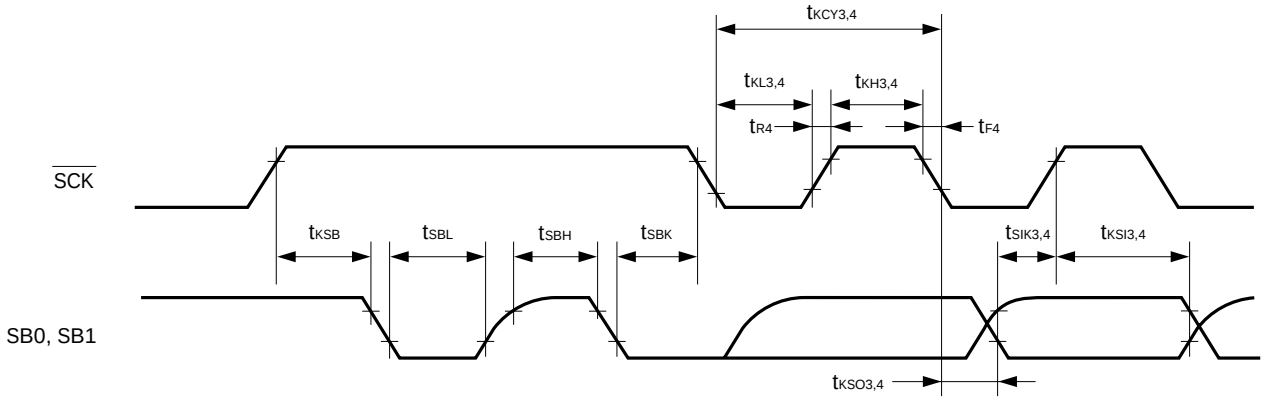
3-wire serial I/O m ode:

★



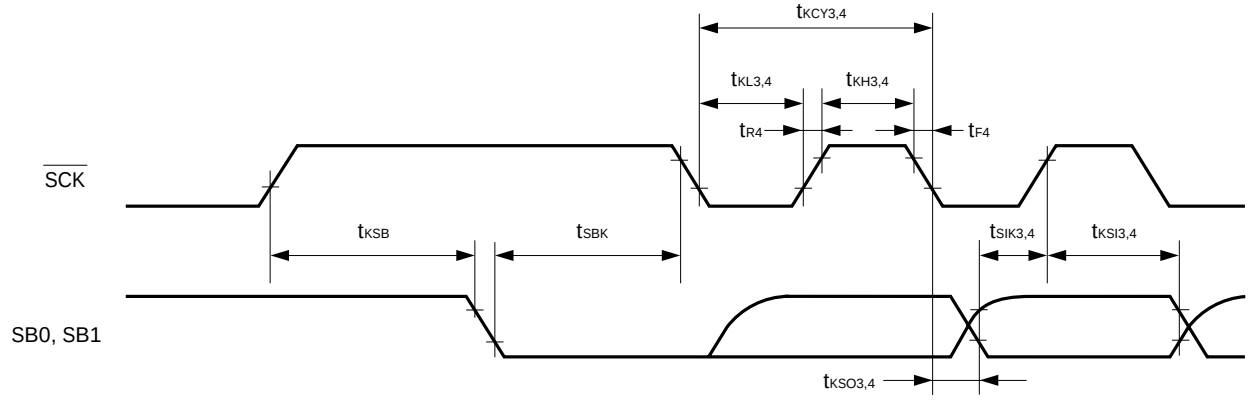
SBI mode (Bus release signal transfer):

★

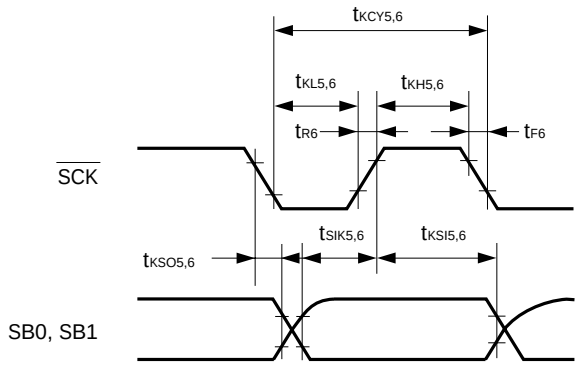


SBI Mode (command signal transfer):

★



2-wire serial I/O mode:



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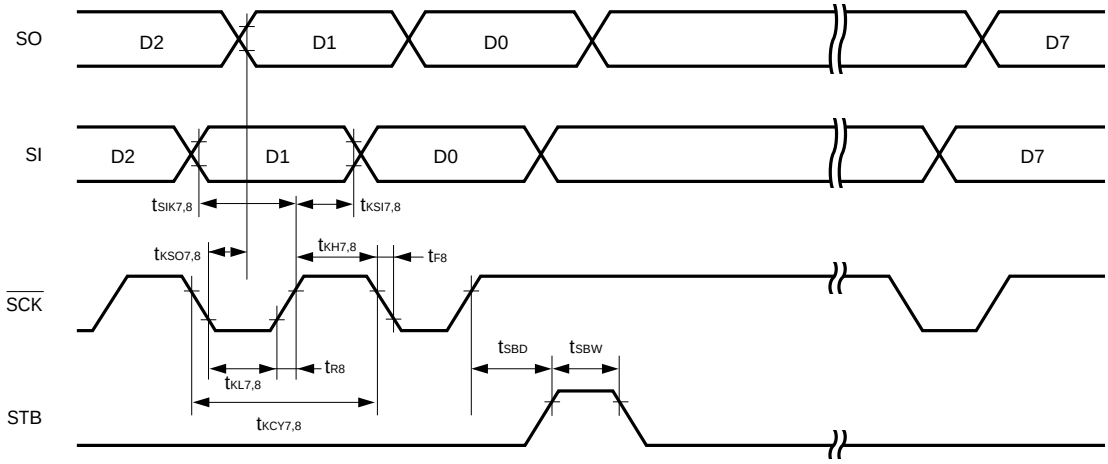
3-wire serial I/O mode with automatic transmit/receive function:



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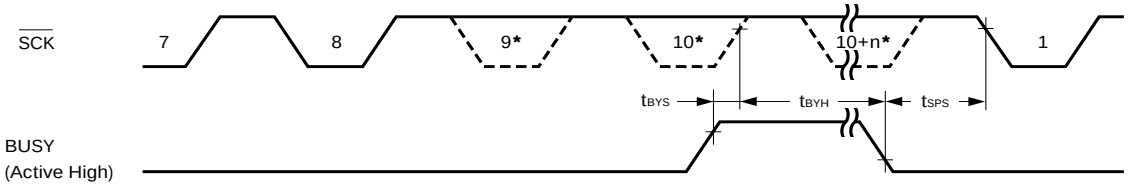
3-wire serial I/O mode with automatic transmit/receive function (busy processing):



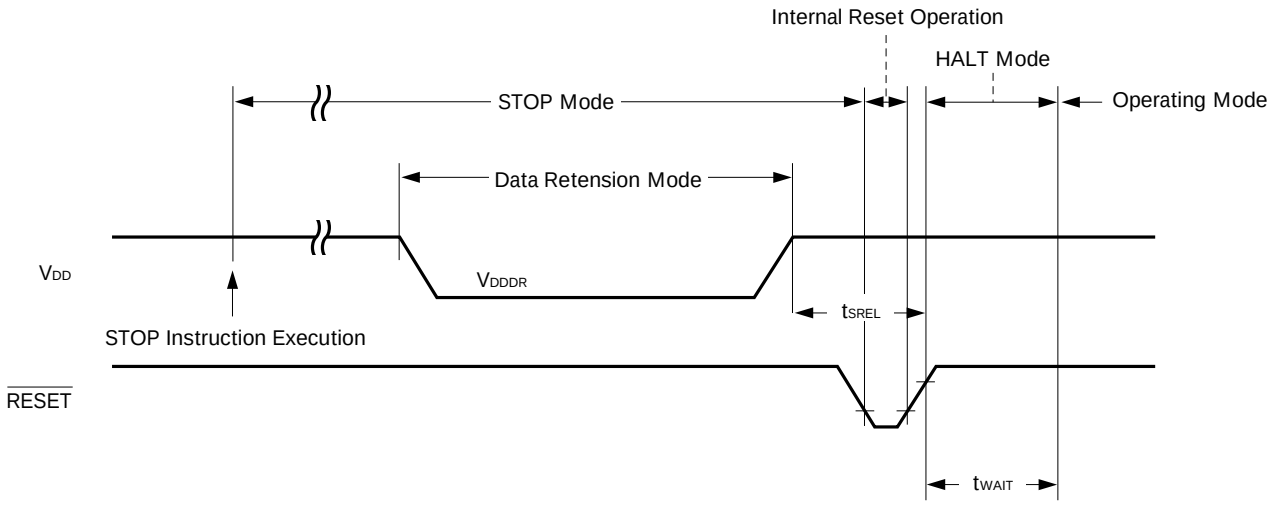
***** The signal is not actually driven low here; it is shown as such to indicate the timing.

Data Memory Stop Mode Low Supply Voltage Data Retention Characteristics (Ta = –40 to +85 °C)

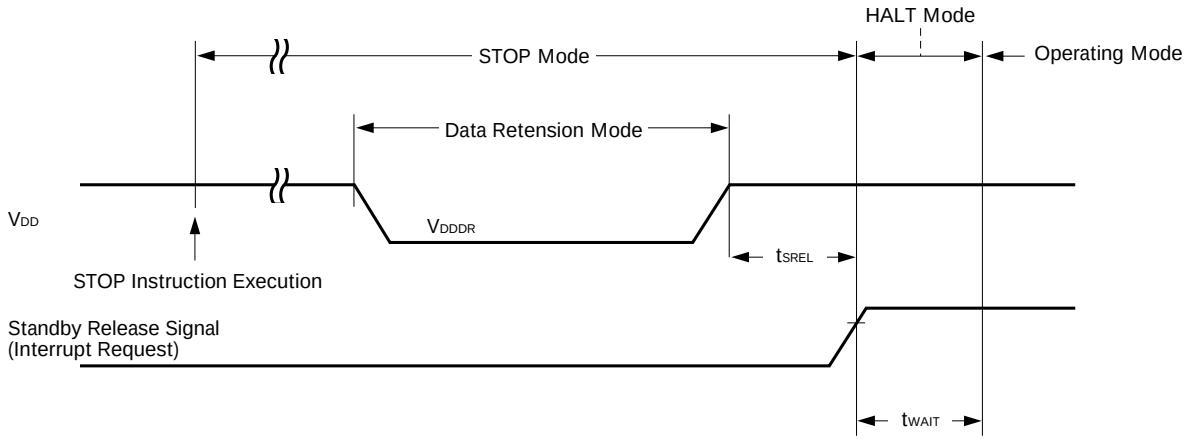
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		2.0		6.0	V
Data retention supply current	I_{DDDR}	V_{DDDR} = 2.0 V Subsystem clock stop and feed-back resister disconnected		0.1	10	μA
Release signal set time	t_{SREL}		0			μs
Oscillation stabilization wait time	t_{WAIT}	Release by $\overline{\text{RESET}}$		2^{18}/fx		ms
		Release by interrupt		*		ms

* In combination with bit 0 to bit 2 (OSTS0 to OSTS2) of oscillation stabilization time select register, selection of 2^{13}/fx and 2^{15}/fx to 2^{18}/fx is possible.

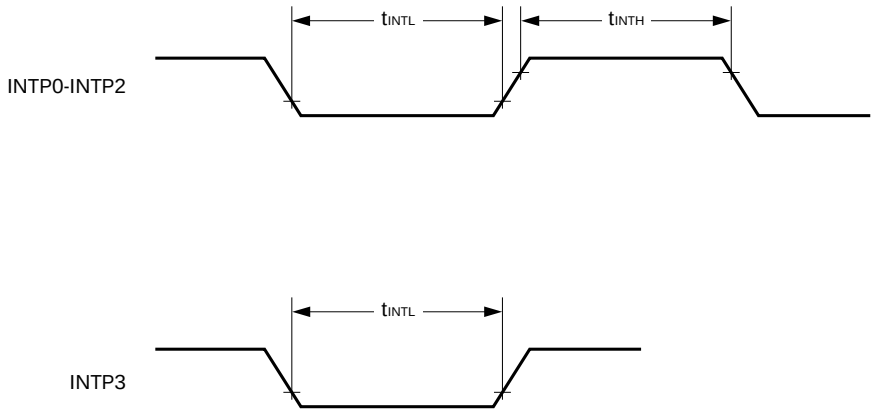
Data Retention Timing (STOP Mode Release by $\overline{\text{RESET}}$)



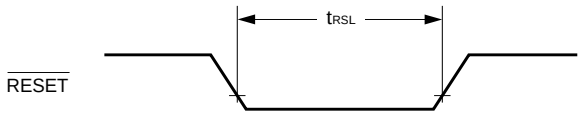
Data Retention Timing (Standby Release Signal : STOP Mode Release by Interrupt Signal)



Interrupt Input Timing

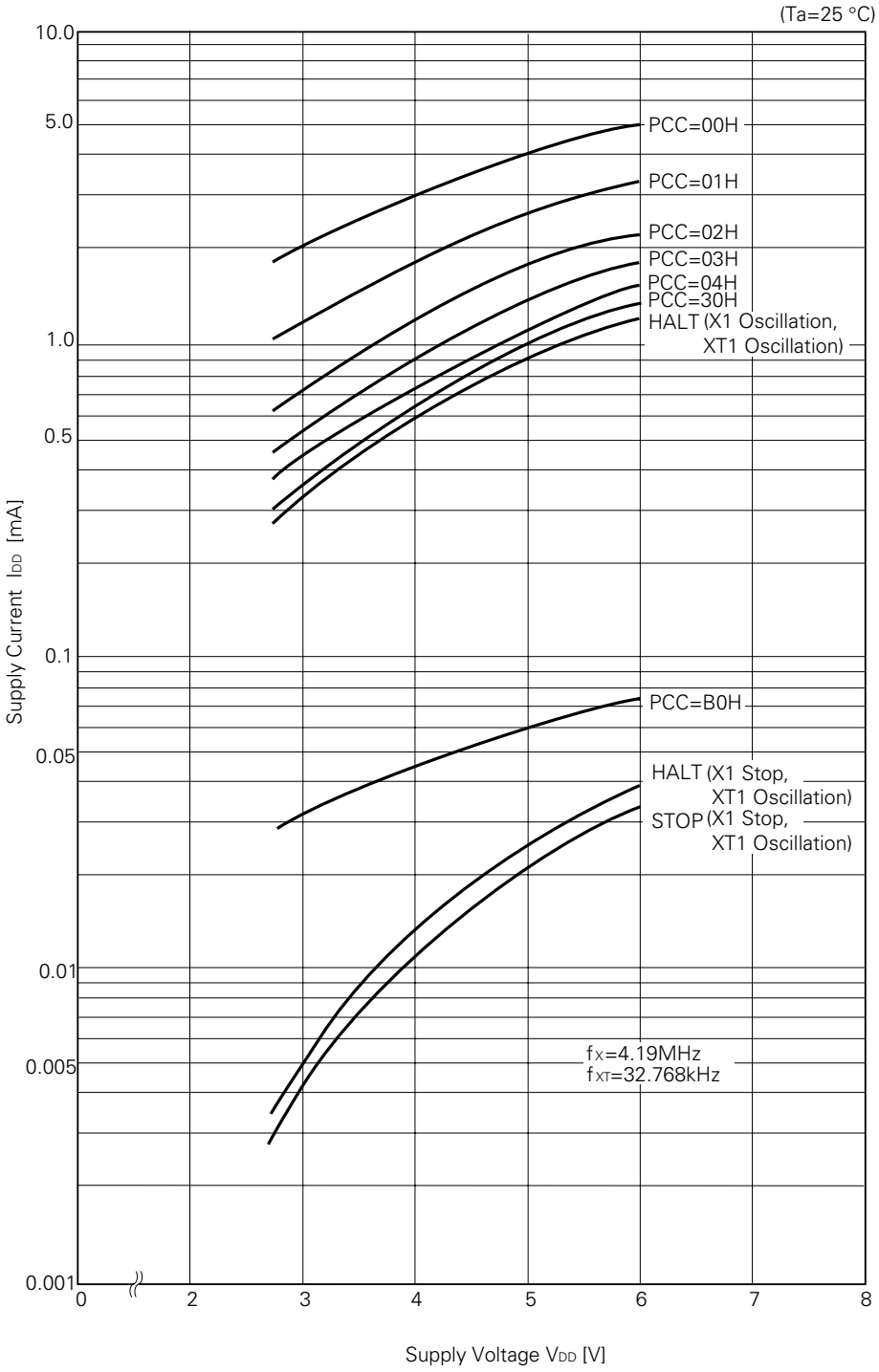


$\overline{\text{RESET}}$ Input Timing

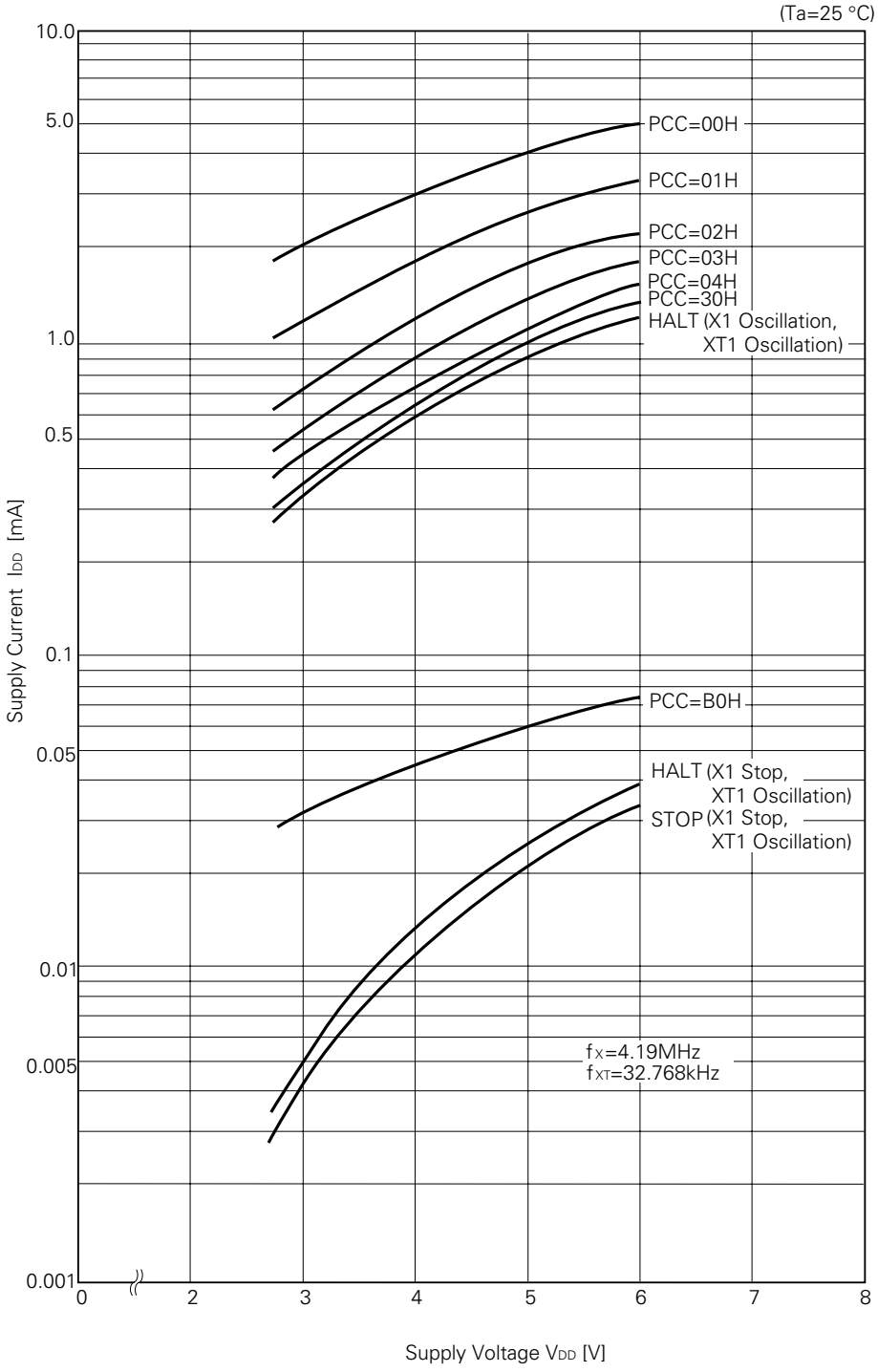


12. CHARACTERISTIC CURVE (REFERENCE VALUES)

I_{DD} vs V_{DD} (Main System Clock: 8.38 MHz)

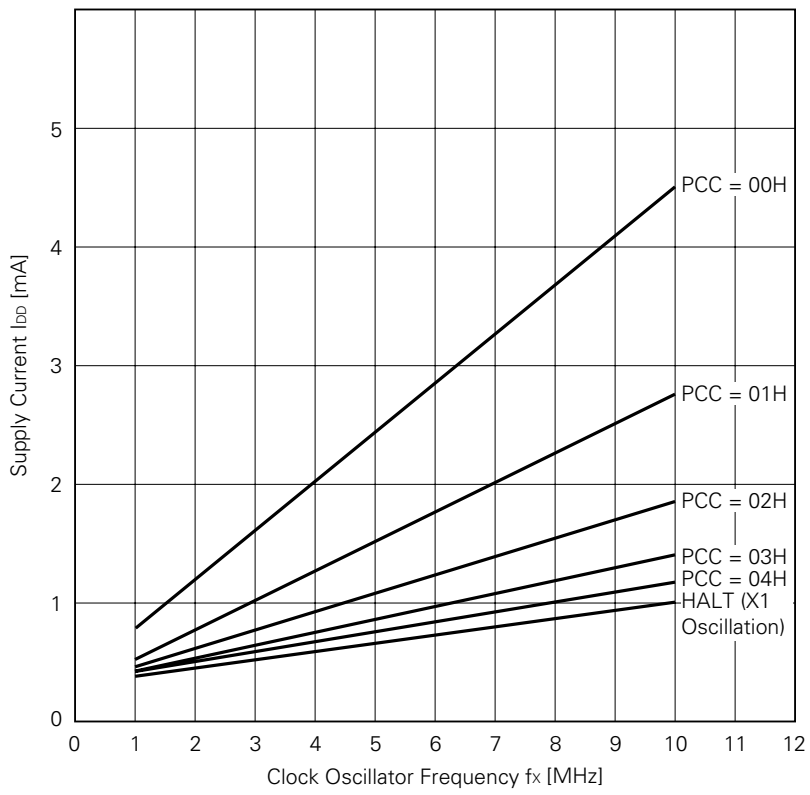


I_{DD} vs V_{DD} (Main System Clock: 4.19 MHz)



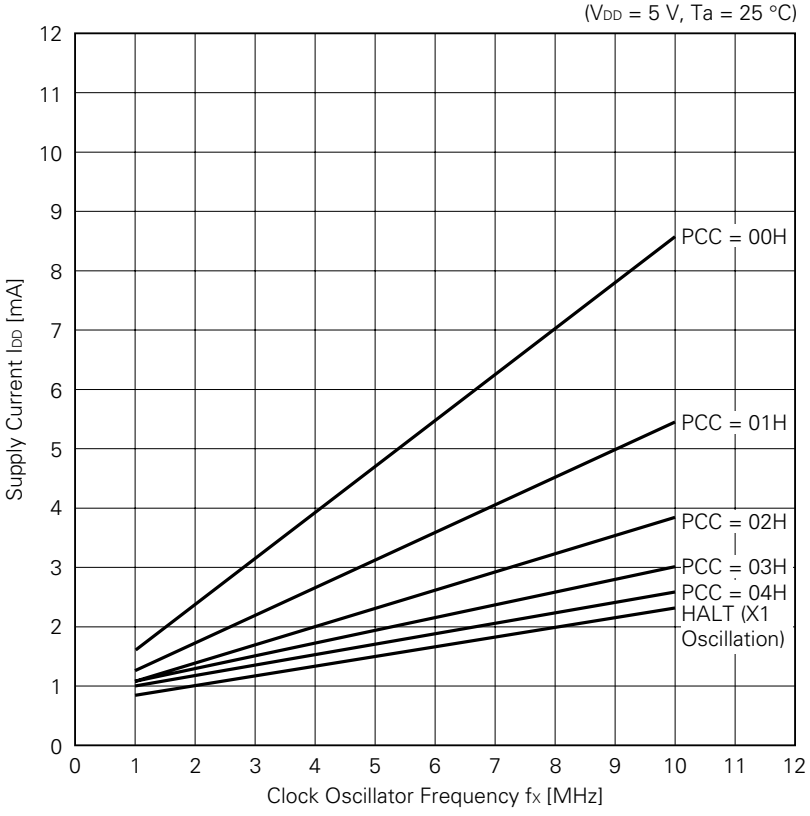
I_{DD} vs f_X

(V_{DD} = 3 V, Ta = 25 °C)

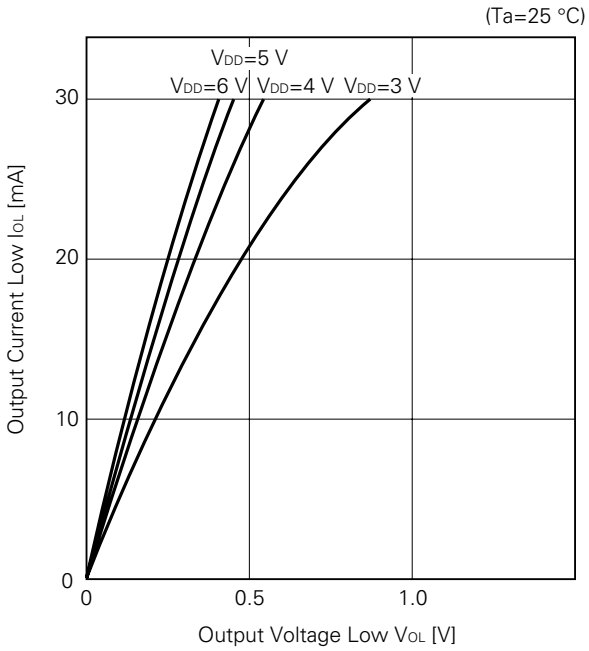


I_{DD} vs f_X

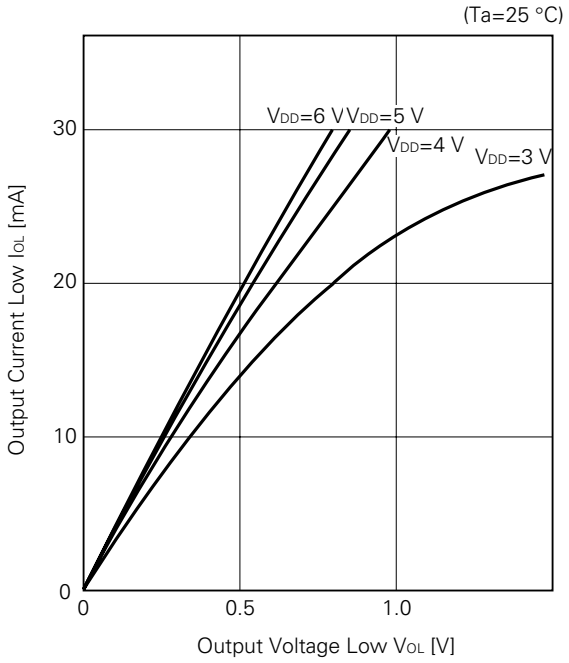
(V_{DD} = 5 V, Ta = 25 °C)



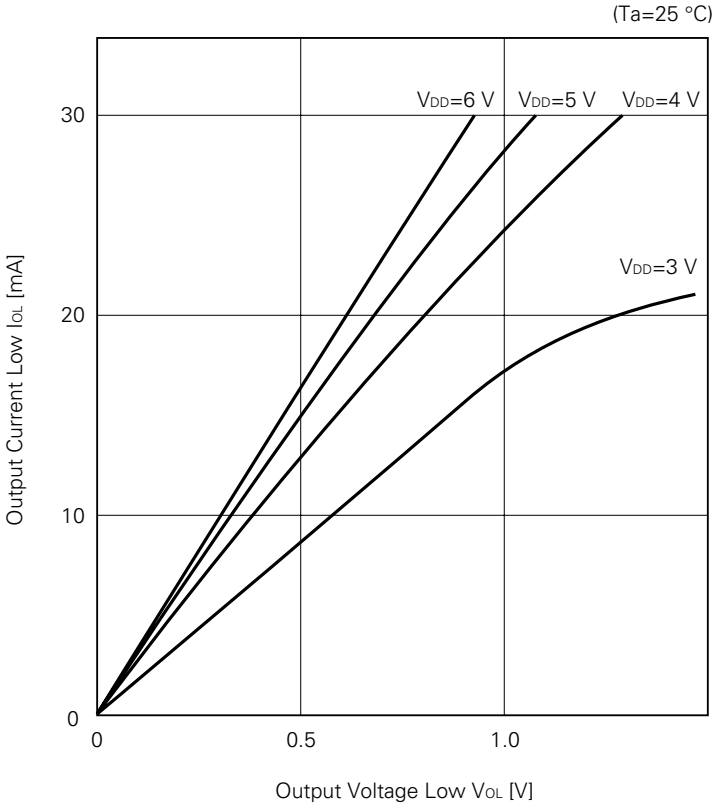
V_{OL} vs I_{OL} (Port 0, 2 to 5, P64 to P67)



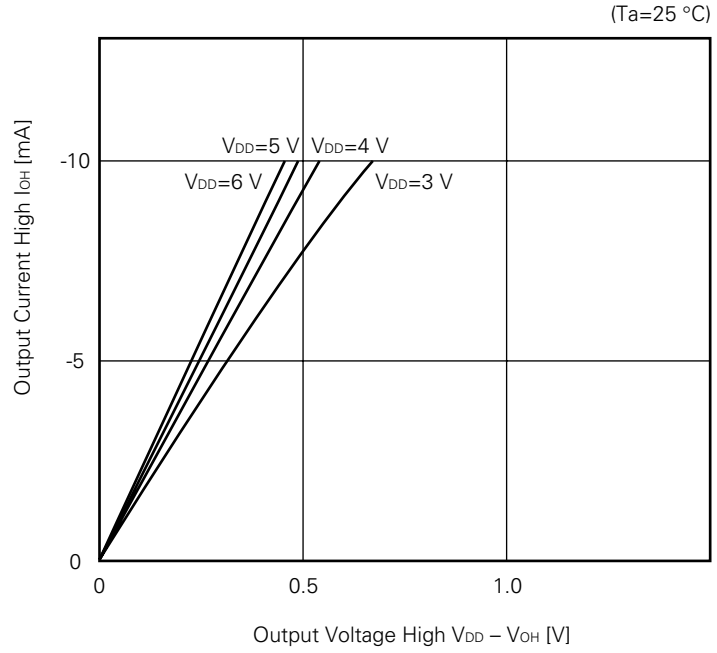
V_{OL} vs I_{OL} (Port 1)



V_{OL} vs I_{OL} (P60 to P63)



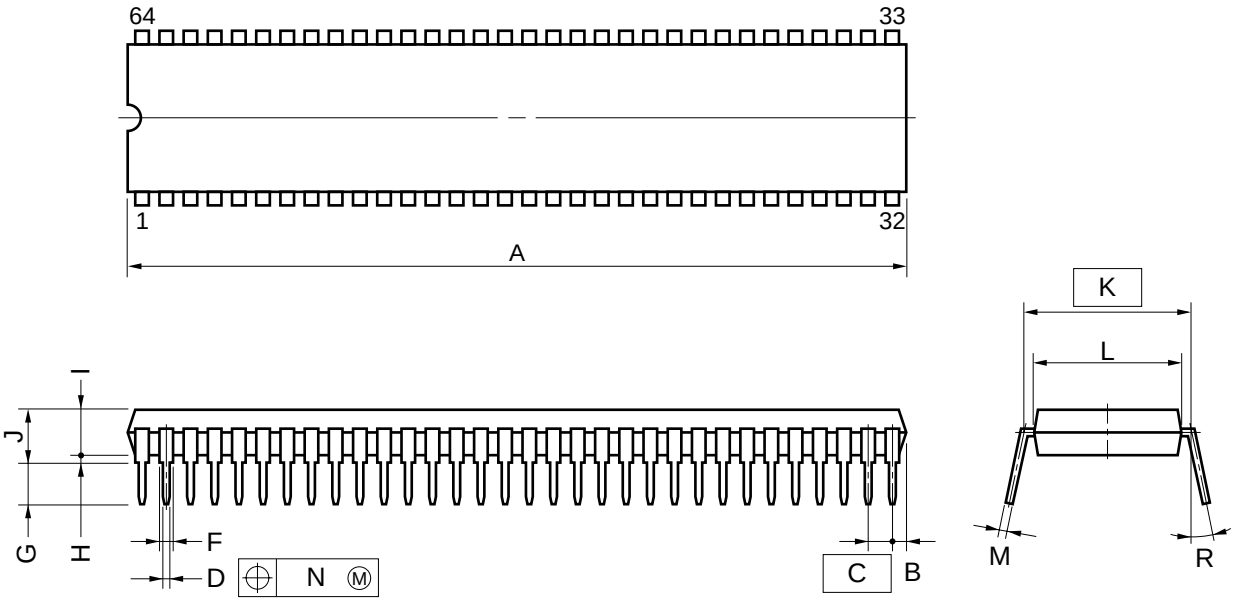
V_{OH} vs I_{OH} (Port 0 to 5, P64 to P67)



13. PACKAGE INFORMATION

DRAWINGS OF MASS-PRODUCTION PRODUCT PACKAGES (1/2)

64 PIN PLASTIC SHRINK DIP (750 mil)



NOTE

1) Each lead centerline is located within 0.17 mm (0.007 inch) of its true position (T.P.) at maximum material condition.
2) Item "K" to center of leads when formed parallel.

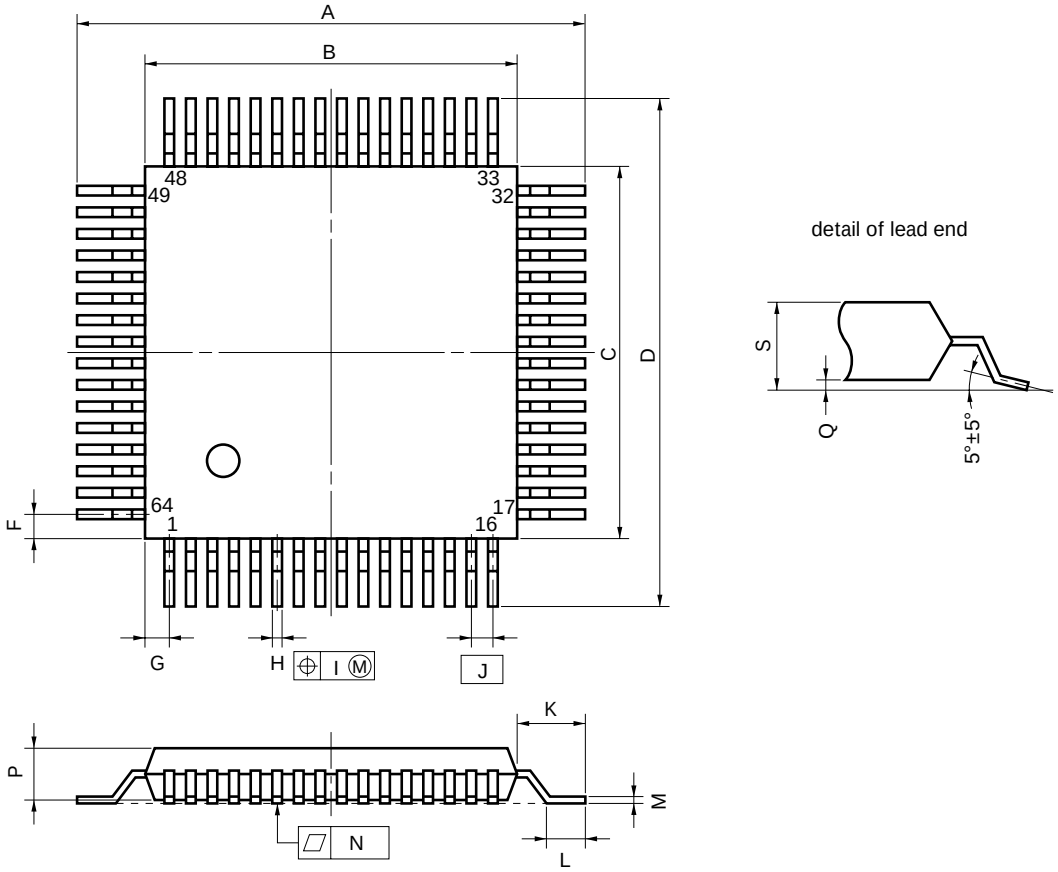
ITEM	MILLIMETERS	INCHES
A	58.68 MAX.	2.311 MAX.
B	1.78 MAX.	0.070 MAX.
C	1.778 (T.P.)	0.070 (T.P.)
D	0.50 ± 0.10	$0.020^{+0.004}_{-0.005}$
F	0.9 MIN.	0.035 MIN.
G	3.2 ± 0.3	0.126 ± 0.012
H	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.08 MAX.	0.200 MAX.
K	19.05 (T.P.)	0.750 (T.P.)
L	17.0	0.669
M	$0.25^{+0.10}_{-0.05}$	$0.010^{+0.004}_{-0.003}$
N	0.17	0.007
R	0~15°	0~15°

P64C-70-750A,C-1

Caution Dimensions and materials of ES products are different from those of mass-production products. Refer to DRAWINGS OF ES PRODUCT PACKAGES (1/2). ★

DRAWINGS OF MASS-PRODUCTION PRODUCT PACKAGES (2/2)

64 PIN PLASTIC QFP (□14)



P64GC-80-AB8-3

NOTE

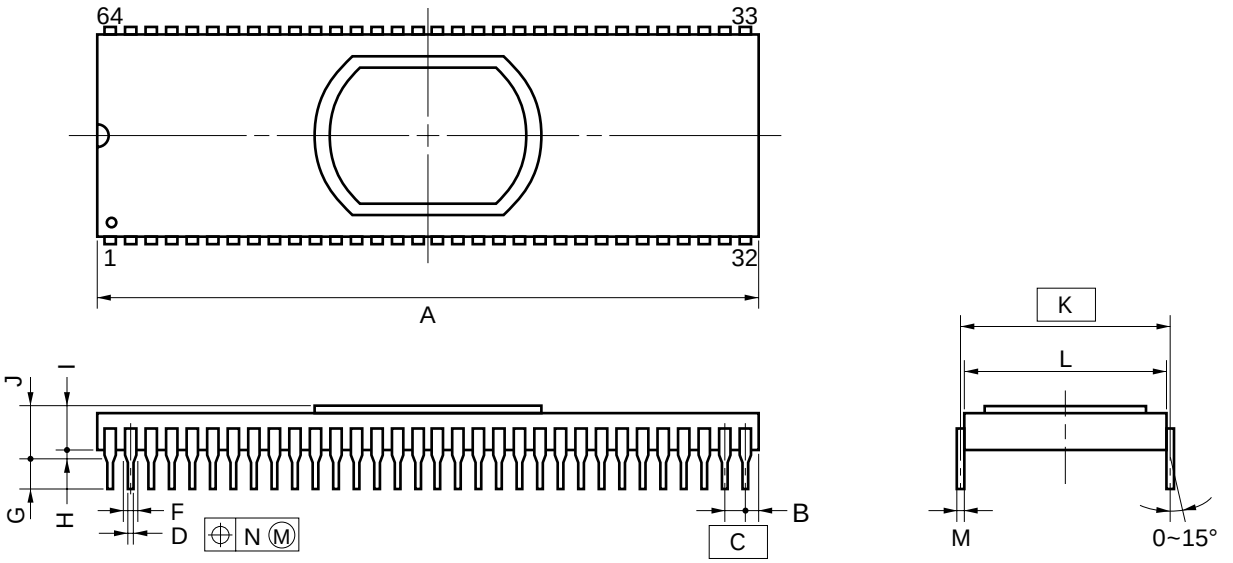
Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	17.6±0.4	0.693±0.016
B	14.0±0.2	$0.551^{+0.009}_{-0.008}$
C	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	17.6±0.4	0.693±0.016
F	1.0	0.039
G	1.0	0.039
H	0.35±0.10	$0.014^{+0.004}_{-0.005}$
I	0.15	0.006
J	0.8 (T.P.)	0.031 (T.P.)
K	1.8±0.2	0.071±0.008
L	0.8±0.2	$0.031^{+0.009}_{-0.008}$
M	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
P	2.55	0.100
Q	0.1±0.1	0.004±0.004
S	2.85 MAX.	0.112 MAX.

Caution Dimensions and materials of ES products are different from those of mass-production products. Refer to DRAWINGS OF ES PRODUCT PACKAGES (2/2).

DRAWINGS OF ES PRODUCT PACKAGES (1/2)

64PIN CERAMIC SHRINK DIP (SEAM WELD) (750 mil)



P64D-70-750A1

NOTES

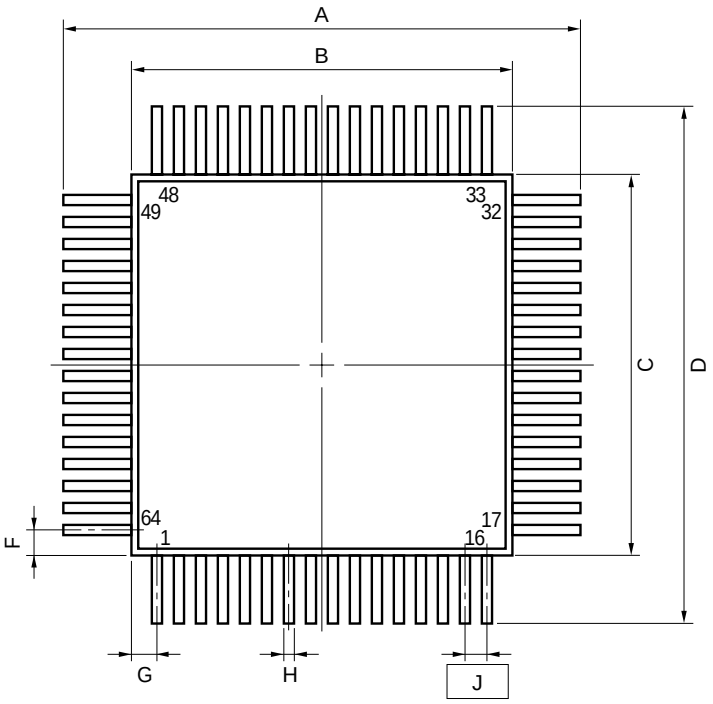
1) Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.

2) Item "K" to center of leads when formed parallel.

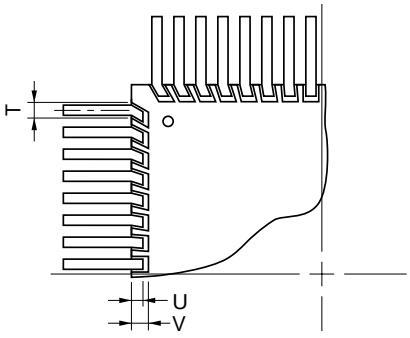
ITEM	MILLIMETERS	INCHES
A	58.16 MAX.	2.290 MAX.
B	1.521 MAX.	0.060 MAX.
C	1.778 (T.P.)	0.070 (T.P.)
D	0.46±0.05	0.018±0.002
F	0.8 MIN.	0.031 MIN.
G	3.5±0.3	0.138±0.012
H	1.02 MIN.	0.040 MIN.
I	3.14	0.124
J	5.08 MAX.	0.200 MAX.
K	19.05 (T.P.)	0.750 (T.P.)
L	18.8	0.740
M	0.25±0.05	$0.010^{+0.002}_{-0.003}$
N	0.25	0.01

DRAWINGS OF ES PRODUCT PACKAGES (2/2)

64 PIN CERAMIC QFP (14 × 14) (FOR ES)



(Bottom View)



X64B-80A-1

ITEM	MILLIMETERS	INCHES
A	22.0±0.4	0.866±0.016
B	14.0	0.551
C	14.0	0.551
D	22.0±0.4	0.866±0.016
F	1.0	0.039
G	1.0	0.039
H	0.32	0.013
J	0.8 (T.P.)	0.031 (T.P.)
K	4.0±0.15	$0.157^{+0.007}_{-0.006}$
M	0.25	0.01
Q	3.0 MAX.	0.119 MAX.
T	0.55	0.022
U	1.0	0.039
V	1.2	0.047

14. RECOMMENDED SOLDERING CONDITIONS ★

The μPD78011B/78012B/78013/78014 should be soldered and mounted under the conditions recommended in the table below.

For detail of recommended soldering conditions, refer to the information document **"Semiconductor Device Mounting Technology Manual" (IE-1207)**.

For soldering methods and conditions other than those recommended below, contact our salespersonnel.

Table 14-1 Surface Mounting Type Soldering Conditions

(1) μPD78011BGC-×××-AB8: 64-Pin Plastic QFP (□14 mm)
μPD78012BGC-×××-AB8: 64-Pin Plastic QFP (□14 mm)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Duration: 30 sec. max. (at 210°C or above), Number of times: Twice max. < Points to note > (1) Start the second reflow after the device temprature by the first reflow returns to normal. (2) Flux washing by the water after the first reflow should be avoided.	IR35-00-2
VPS	Package peak temperature: 215°C, Duration: 40 sec. max. (at 200°C or above) Number of times: Twice max. < Points to note > (1) Start the second reflow after the device temprature by the first reflow returns to normal. (2) Flux washing by the water after the first reflow should be avoided.	VP15-00-2
Pin part heating	Pin temperature: 300°C max., Duration: 3 sec. max. (per device side)	—

(2) μPD78013GC-×××-AB8 : 64-Pin Plastic QFP (□14 mm)
μPD78014GC-×××-AB8 : 64-Pin Plastic QFP (□14 mm)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Duration: 30 sec. max. (at 210°C or above), Number of times: Twice < Points to note > (1) Start the second reflow after the device temprature by the first reflow returns to normal. (2) Flux washing by the water after the first reflow should be avoided.	IR35-00-2
VPS	Package peak temperature: 215°C, Duration: 40 sec. max. (at 200°C or above), Number of times: Twice < Points to note > (1) Start the second reflow after the device temprature by the first reflow returns to normal. (2) Flux washing by the water after the first reflow should be avoided.	VP15-00-2
Wave soldering	Solder bath temperature: 260°C max. Duration: 10 sec. max. Number of times: Once Preliminary heat temperature: 120°C max. (Package surface temperature)	WS60-00-1
Pin part heating	Pin temperature: 300°C max., Duration: 3 sec. max. (per device side)	—

Caution Use more than one soldering method should be avoided (except in the case of pin part heating).

Table 14-2 Insertion Type Soldering Conditions

μPD78011BCW-××× : 64-Pin Plastic Shrink DIP (750 mil)
μPD78012BCW-××× : 64-Pin Plastic Shrink DIP (750 mil)
μPD78013CW-××× : 64-Pin Plastic Shrink DIP (750 mil)
μPD78014CW-××× : 64-Pin Plastic Shrink DIP (750 mil)

Soldering Method	Soldering Conditions
Wave soldering (pin only)	Solder bath temperature: 260°C max., Duration: 10 sec. max.
Pin part heating	Pin temperature: 300°C max., Duration: 3 sec. max. (per pin)

Caution Wave soldering is only for the lead part in order that jet solder can not contact with the chip directly.

APPENDIX A. DEVEROPMENT TOOLS

The following development tools are available for system development using the μPD78011B, 78012B, 78013, 78014.

Language Processing Software

RA78K/0*1, 2, 3	78K/0 series common assembler package
CC78K/0*1, 2, 3	78K/0 series common C compiler package
DF78014*1, 2, 3	μPD78014 subseries device file ★
CC78K/0-L*1, 2, 3	78K/0 series common C compiler library source file

PROM Writting Tools

PG-1500	PROM programmer
PA-78P014CW PA-78P014GC	Programmer adapter connected to PG-1500
PG-1500 controller*1, 2	PG-1500 control program

Debugging Tool

IE-78000-R	78K/0 series common in-circuit emulator
IE-78000-R-BK	78K/0 series common break board
IE-78014-R-EM	μPD78002/78014 subseries evaluation emulation board
EP-78240CW-R EP-78240GC-R	Emulation probe common to μPD78244 subseries
EV-9200GC-64	Socket to be mounted on user system board created for the 64-pin plastic QFP
SD78K/0*1, 2	IE-78000-R screen debugger
SM78K/0*4, 5, 6	78K/0 series common system simulator ★
DF78014*1, 2, 4, 5	μPD78014 subseries device file

Real-Time OS

RX78K/0*1, 2, 3	78K/0 series common real-time OS
MX78K/0*1, 2, 3, 6	78K/0 series common OS ★

Fuzzy Inference Devleopment Support System

FE9000*1/FE9200*5	Fuzzy knowledge data creation tool
FT9080*1/FT9085*2	Translator
FI78K0*1, 2	Fuzzy inference module
FD78K0*1, 2	Fuzzy inference debugger

* **1.** PC-9800 series (MS-DOS™) based
2. IBM PC/AT™ (PC DOS™) based
3. HP9000 series 300™, HP9000 series 700™ (HP-UX™) based, SPARCstation™, (SunOS™) based, EWS-4800 series (EWS-UX/V) based ★

4. PC-9800 series (MS-DOS + Windows™) based
5. IBM PC/AT (PC DOS + Windows) based
6. Under development

Remarks 1. For development tools manufactured by a third party, see the **"78K/0 Series Selection Guide" (IF-1185).**

★ 2. RA78K/0, CC78K/0, SD78K/0, and SM78K/0 are used in combination with DF78014.

APPENDIX B. RELATED DOCUMENTS ★

Device Related Documents

Document Name		Document No. (Japanese)	Document No. (English)
User's Manual		IEU-780	IEU-1314
78K/0 Series User's Manual - Instruction		IEU-849	IEU-1372
Application Note	Basic I	IEA-715	IEA-1288
	Basic II	IEA-740	IEA-1299
	Floating-Point Arithmetic Program	IEA-718	IEA-1289
	Electronic Notebook	IEA-744	IEA-1301

Development Tools Documents (User's Manual)

Document Name		Document No. (Japanese)	Document No. (English)
RA78K Series Assembler Package	Operation	EEU-809	EEU-1399
	Language	EEU-815	EEU-1404
RA78K Series Structured Assembler Preprocessor		EEU-817	EEU-1402
CC78K Series C Compiler	Operation	EEU-656	EEU-1280
	Language	EEU-655	EEU-1284
PG-1500 PROM Programmer		EEU-651	EEU-1335
PG-1500 Controller		EEU-704	EEU-1291
IE-78000-R		EEU-810	EEU-1398
IE-78000-R-BK		EEU-867	EEU-1427
IE-78014-R-EM		EEU-805	EEU-1400
SD78K/0 Screen Debugger	Basic	EEU-852	EEU-1414
	Reference	EEU-816	EEU-1413

Caution The contents of the above related documents are subject to change without notice. The latest documents should be used for design, etc.

Embedded Software Documents (User's Manual)

Document Name	Document No. (Japanese)	Document No. (English)
Fuzzy Knowledge Data Creation Tool	EEU-829	EEU-1438
78K/0, 78K/II, 87AD Series Fuzzy Inference Development Support System - Translator	EEU-862	EEU-1444

Other Documents

Document Name	Document No. (Japanese)	Document No. (English)
Package Manual	IEI-635	IEI-1213
Semiconductor Device Mounting Technology Manual	IEI-616	IEI-1207
Quality Grade on NEC Semiconductor Devices	IEI-620	IEI-1209
Semiconductor Devices Quality Guarantee Guide	MEI-603	MEI-1202

Caution The contents of the above related documents are subject to change without notice. The latest documents should be used for design, etc.

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

M4 92.6